

具有三态输出寄存器的 SN74LV595A 8 位移位寄存器

1 特性

- V_{CC} 工作范围为 2V 至 5.5V
- 5V 时 t_{pd} 最大值为 7.1ns
- $V_{CC} = 3.3V$ 、 $T_A = 25^\circ C$ 时, V_{OLP} (输出接地反弹) 典型值小于 0.8V
- $V_{CC} = 3.3V$ 、 $T_A = 25^\circ C$ 时, V_{OHV} (输出 V_{OH} 下冲) 典型值大于 2.3V
- 支持所有端口上的混合模式电压运行
- 8 位串行输入/并行输出移位寄存器
- I_{off} 支持带电插入、局部关断模式和后驱动保护
- 移位寄存器具有直接清零功能
- 闩锁性能超过 250mA, 符合 JESD 17 规范

2 应用

- 输出扩展
- LED 矩阵控制
- 7 段显示控制

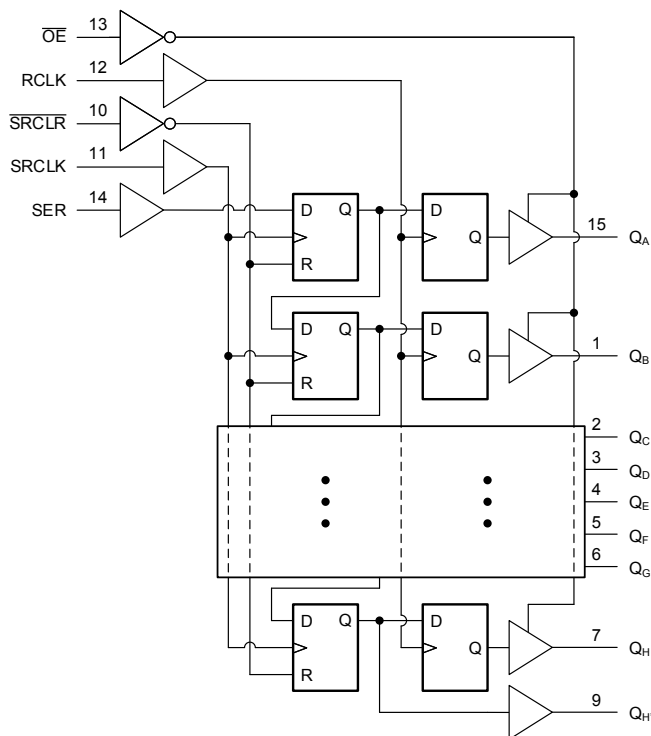
3 说明

SN74LV595A 器件包含一个对 8 位 D 类存储寄存器进行馈送的 8 位串行输入、并行输出移位寄存器。移位寄存器时钟 (SRCLK) 和存储寄存器时钟 (RCLK) 均为正边沿触发。

封装信息⁽¹⁾

器件型号	封装	封装尺寸 (标称值)
SN74LV595A	RGY (VQFN, 16)	4.00mm × 3.50mm
	PW (TSSOP, 16)	5.00mm × 4.40mm
	NS (SO, 16)	10.20mm × 5.30mm
	D (SOIC, 16)	9.00 mm × 3.90 mm
	BQB (WQFN, 16)	3.60mm × 2.60mm

(1) 如需了解所有可用封装, 请参阅数据表末尾的可订购产品附录。



逻辑图 (正逻辑)



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4 Revision History

注：以前版本的页码可能与当前版本的页码不同

Changes from Revision S (November 2022) to Revision T (March 2023)	Page
• 根据当前标准更新了文档的结构布局.....	1
• Updated thermal values for NS package from $R_{\theta JA} = 79.4$ to 110.8 , $R_{\theta JC(top)} = 35.8$ to 72 , $R_{\theta JB} = 40.2$ to 72.6 , $\Psi_{JT} = 5.5$ to 39.7 , $\Psi_{JB} = 39.9$ to 72.3 , all values in $^{\circ}\text{C/W}$	5

Changes from Revision R (June 2022) to Revision S (November 2022)	Page
• 将数据表的状态从 预告信息 更改为 量产数据	1

5 Pin Configuration and Functions

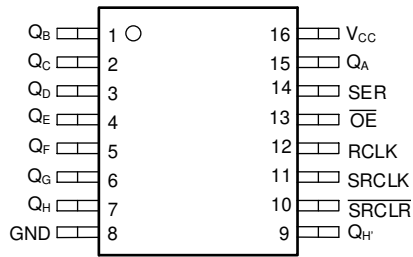


图 5-1. D, DW, or PW Package,
16-Pin SOIC, SOP or TSSOP
(Top View)

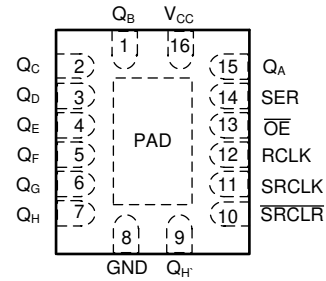


图 5-2. BQB or RGY Package,
16-Pin WQFN or VQFN
(Transparent Top View)

表 5-1. Pin Functions

PIN		TYPE ⁽¹⁾	DESCRIPTION
NAME	NO.		
GND	8	G	Ground Pin
OE	13	I	Output Enable Pin. Active LOW
QA	15	O	QA Output
QB	1	O	QB Output
QC	2	O	QC Output
QD	3	O	QD Output
QE	4	O	QE Output
QF	5	O	QF Output
QG	6	O	QG Output
QH	7	O	QH Output
QH'	9	O	QH' Output
RCLK	12	I	RCLK Input
SER	14	I	SER Input
SRCLK	11	I	SRCLK Input
SRCLR	10	I	SRCLR Input
VCC	16	P	Power Pin
Thermal Pad		—	Thermal Pad ⁽²⁾

(1) I = Input, O = Output, I/O = Input or Output, G = Ground, P = Power

(2) RGY and BQB package only

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

		MIN	MAX	UNIT
V_{CC}	Supply voltage range	- 0.5	7	V
V_I	Input voltage range ⁽²⁾	- 0.5	7	V
V_O	Voltage range applied to any output in the high-impedance or power-off state ⁽²⁾	- 0.5	7	V
V_O	Output voltage range applied in the high or low state ^{(2) (3)}	- 0.5	$V_{CC} + 0.5$	V
I_{IK}	Input clamp current	$V_I < 0$		- 20 mA
I_{OK}	Output clamp current	$V_O < 0$		- 50 mA
I_O	Continuous output current	$V_O = 0$ to V_{CC}		± 35 mA
	Continuous current through V_{CC} or GND			± 70 mA
T_{stg}	Storage temperature range	- 65	150	°C

(1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) The input and output negative-voltage ratings may be exceeded if the input and output current ratings are observed.

(3) This value is limited to 5.5-V maximum.

6.2 ESD Ratings

		VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge		
	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	± 2000	V
	Machine Model (MM), per JEDEC specification	± 200	
	Charged-device model (CDM), per ANSI/ESDA/JEDEC JS-002 ⁽²⁾	± 1000	

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

			MIN	MAX	UNIT
V _{CC}	Supply voltage		2	5.5	V
V _{IH}	High-level input voltage	V _{CC} = 2 V	1.5		V
		V _{CC} = 2.3 V to 2.7 V	V _{CC} × 0.7		
		V _{CC} = 3 V to 3.6 V	V _{CC} × 0.7		
		V _{CC} = 4.5 V to 5.5 V	V _{CC} × 0.7		
V _{IL}	Low-level input voltage	V _{CC} = 2 V		0.5	V
		V _{CC} = 2.3 V to 2.7 V		V _{CC} × 0.3	
		V _{CC} = 3 V to 3.6 V		V _{CC} × 0.3	
		V _{CC} = 4.5 V to 5.5 V		V _{CC} × 0.3	
V _I	Input voltage		0	5.5	V
V _O	Output voltage	High or low state	0	V _{CC}	V
		3-state	0	5.5	
I _{OH}	High-level output current	V _{CC} = 2 V		- 50	μA
		V _{CC} = 2.3 V to 2.7 V		- 2	mA
		V _{CC} = 3 V to 3.6 V		- 8	
		V _{CC} = 4.5 V to 5.5 V		- 16	
I _{OL}	Low-level output current	V _{CC} = 2 V		50	μA
		V _{CC} = 2.3 V to 2.7 V		2	mA
		V _{CC} = 3 V to 3.6 V		8	
		V _{CC} = 4.5 V to 5.5 V		16	
Δt / Δv	Input transition rise or fall rate	V _{CC} = 2.3 V to 2.7 V		200	ns/V
		V _{CC} = 3 V to 3.6 V		100	
		V _{CC} = 4.5 V to 5.5 V		20	
T _A	Operating free-air temperature		- 40	125	°C

(1) All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, [Implications of Slow or Floating CMOS Inputs](#).

6.4 Thermal Information

THERMAL METRIC ⁽¹⁾		SN74LV595A						UNIT
		D	DB	NS	PW	RGY	BQB	
		16 PINS	16 PINS	16 PINS	16 PINS	16 PINS	16 PINS	
R _{θJA}	Junction-to-ambient thermal resistance	80.2	97.8	110.8	131.2	39.5	85.9	°C/W
R _{θJC(top)}	Junction-to-case (top) thermal resistance	40.3	48.1	72	69.4	50.5	82.4	
R _{θJB}	Junction-to-board thermal resistance	38.0	48.5	72.6	75.8	17.1	55.6	
ψ _{JT}	Junction-to-top characterization parameter	9.0	10.0	39.7	21	0.9	9.4	
ψ _{JB}	Junction-to-board characterization parameter	37.7	47.9	72.3	75.4	17.2	55.6	
R _{θJC(bot)}	Junction-to-case (bottom) thermal resistance	N/A	N/A	N/A	N/A	5.9	33.3	

(1) For more information about traditional and new thermal metrics, see the *IC Package Thermal Metrics* application report ([SPRA953](#)).

6.5 Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		V _{CC}	- 40°C to 85°C			- 40°C to 125°C			UNIT
				MIN	TYP	MAX	MIN	TYP	MAX	
V _{OH}		I _{OH} = - 50 μA	2 V to 5.5 V	V _{CC} - 0.1			V _{CC} - 0.1			V
		I _{OH} = - 2 mA	2.3 V	2			2			
	Q _H '	I _{OH} = - 6 mA	3 V	2.48			2.45			
	Q _A - Q _H	I _{OH} = - 8 mA		2.48			2.45			
	Q _H '	I _{OH} = - 12 mA	4.5 V	3.8			3.7			
	Q _A - Q _H	I _{OH} = - 16 mA		3.8			3.7			
V _{OL}		I _{OL} = 50 μA	2 V to 5.5 V	0.1			0.1			V
		I _{OL} = 2 mA	2.3 V	0.4			0.4			
	Q _H '	I _{OL} = 6 mA	3 V	0.44			0.5			
	Q _A -Q _H	I _{OL} = 8 mA		0.44			0.5			
	Q _H '	I _{OL} = 12 mA	4.5 V	0.55			0.6			
	Q _A -Q _H	I _{OL} = 16 mA		0.55			0.6			
I _I	V _I = 5.5 V or GND		0 V to 5.5 V	±1			±1			μA
I _{OZ}	V _O = V _{CC} or GND	Q _A - Q _H	5.5 V	±5			±5			μA
I _{CC}	V _I = V _{CC} or GND	I _O = 0	5.5 V	20			20			μA
I _{off}	V _I or V _O = 0 to 5.5 V		0 V	5			5			μA
C _i	V _I = V _{CC} or GND		3.3 V	3.5			3.5			pF

6.6 Timing Requirements, $V_{CC} = 2.5 \text{ V} \pm 0.2 \text{ V}$

over recommended operating free-air temperature range (unless otherwise noted) (see 图 7-1)

			T _A = 25°C		– 40°C to 85°C		– 40°C to 125°C		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
t _w	Pulse duration	SRCLK high or low	7		7.5		8.5		ns
		RCLK high or low	7		7.5		8.5		
		SRCLR low	6		6.5		7.5		
t _{su}	Setup time	SER before SRCLK ↑	5.5		5.5		6.5		ns
		SRCLK ↑ before RCLK ↑ ⁽¹⁾	8		9		10		
		SRCLR low before RCLK ↑	8.5		9.5		10.5		
		SRCLR high (inactive) before SRCLK ↑	4		4		5		
t _h	Hold time	SER after SRCLK ↑	1.5		1.5		2.5		ns

- (1) This setup time allows the storage register to receive stable data from the shift register. The clocks can be tied together, in which case the shift register is one clock pulse ahead of the storage register.

6.7 Timing Requirements, $V_{CC} = 3.3\text{ V} \pm 0.3\text{ V}$

over recommended operating free-air temperature range (unless otherwise noted) (see 图 7-1)

			T _A = 25°C		– 40°C to 85°C		– 40°C to 125°C		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
t _w	Pulse duration	SRCLK high or low	5.5		5.5		6.5		ns
		RCLK high or low	5.5		5.5		6.5		
		SRCLR low	5		5		6		
t _{su}	Setup time	SER before SRCLK ↑	3.5		3.5		4.5		ns
		SRCLK ↑ before RCLK ↑ ⁽¹⁾	8		8.5		9.5		
		SRCLR low before RCLK ↑	8		9		10		
		SRCLR high (inactive) before SRCLK ↑	3		3		4		
t _h	Hold time	SER after SRCLK ↑	1.5		1.5		2.5		ns

- (1) This setup time allows the storage register to receive stable data from the shift register. The clocks can be tied together, in which case the shift register is one clock pulse ahead of the storage register.

6.8 Timing Requirements, $V_{CC} = 5\text{ V} \pm 0.5\text{ V}$

over recommended operating free-air temperature range (unless otherwise noted) (see 图 7-1)

			T _A = 25°C		- 40°C to 85°C		- 40°C to 125°C		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
t _w	Pulse duration	SRCLK high or low	5		5		6		ns
		RCLK high or low	5		5		6		
		SRCLR low	5.2		5.2		6.2		
t _{su}	Setup time	SER before SRCLK ↑	3		3		4		ns
		SRCLK ↑ before RCLK ↑ ⁽¹⁾	5		5		6		
		SRCLR low before RCLK ↑	5		5		6		
		SRCLR high (inactive) before SRCLK ↑	2.5		2.5		3.5		
t _h	Hold time	SER after SRCLK ↑	2		2		3		ns

- (1) This setup time allows the storage register to receive stable data from the shift register. The clocks can be tied together, in which case the shift register is one clock pulse ahead of the storage register.

6.9 Switching Characteristics, $V_{CC} = 2.5\text{ V} \pm 0.2\text{ V}$

over recommended operating free-air temperature range (unless otherwise noted) (see 图 7-1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	LOAD CAPACITANCE	T _A = 25°C			- 40°C to 85°C		- 40°C to 125°C		UNIT
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
f _{max}			C _L = 15 pF	65	80		45		45		MHz
			C _L = 50 pF	60	70		40		40		
t _{PLH}	RCLK	Q _A - Q _H	C _L = 15 pF		8.4	14.2	1	15.8	1	16.8	ns
t _{PHL}					8.4	14.2	1	15.8	1	16.8	
t _{PLH}	SRCLK	Q _H '			9.4	19.6	1	22.2	1	23.2	
t _{PHL}					9.4	19.6	1	22.2	1	23.2	
t _{PHL}	SRCLR	Q _H '			8.7	14.6	1	16.3	1	17.3	
t _{PZH}	OE	Q _A - Q _H			8.2	13.9	1	15	1	16	
t _{PZL}					10.9	18.1	1	20.3	1	21.3	
t _{PHZ}	OE	Q _A - Q _H			8.3	13.7	1	15.6	1	16.6	
t _{PLZ}					9.2	15.2	1	16.7	1	17.7	
t _{PLH}	RCLK	Q _A - Q _H	C _L = 50 pF		11.2	17.2	1	19.3	1	21.3	ns
t _{PHL}					11.2	17.2	1	19.3	1	21.3	
t _{PLH}	SRCLK	Q _H '			13.1	22.5	1	25.5	1	27.5	
t _{PHL}					13.1	22.5	1	25.5	1	27.5	
t _{PHL}	SRCLR	Q _H '			12.4	18.8	1	21.1	1	23.1	
t _{PZH}	OE	Q _A - Q _H			10.8	17	1	18.3	1	20.3	
t _{PZL}					13.4	21	1	23	1	25	
t _{PHZ}	OE	Q _A - Q _H			12.2	18.3	1	19.5	1	21.5	
t _{PLZ}					14	20.9	1	22.6	1	24.6	

6.10 Switching Characteristics, $V_{CC} = 3.3\text{ V} \pm 0.3\text{ V}$

over recommended operating free-air temperature range (unless otherwise noted) (see 图 7-1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	LOAD CAPACITANCE	T _A = 25°C			- 40°C to 85°C		- 40°C to 125°C		UNIT
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
f _{max}			C _L = 15 pF	80	120		70		70		MHz
			C _L = 50 pF	55	105		50		50		
t _{PLH}	RCLK	Q _A - Q _H	C _L = 15 pF		6	11.9	1	13.5	1	14.5	ns
t _{PHL}					6	11.9	1	13.5	1	14.5	
t _{PLH}	SRCLK	Q _H '			6.6	13	1	15	1	16	
t _{PHL}					6.6	13	1	15	1	16	
t _{PHL}	SRCLR	Q _H '			6.2	12.8	1	13.7	1	14.7	
t _{PZH}	OE	Q _A - Q _H			6	11.5	1	13.5	1	14.5	
t _{PZL}					7.8	11.5	1	13.5	1	14.5	
t _{PHZ}	OE	Q _A - Q _H			6.1	14.7	1	15.2	1	16.2	
t _{PLZ}					6.3	14.7	1	15.2	1	16.2	
t _{PLH}	RCLK	Q _A - Q _H	C _L = 50 pF		7.9	15.4	1	17	1	19	ns
t _{PHL}					7.9	15.4	1	17	1	19	
t _{PLH}	SRCLK	Q _H '			9.2	16.5	1	18.5	1	20.5	
t _{PHL}					9.2	16.5	1	18.5	1	20.5	
t _{PHL}	SRCLR	Q _H '			9	16.3	1	17.2	1	19.2	
t _{PZH}	OE	Q _A - Q _H			7.8	15	1	17	1	19	
t _{PZL}					9.6	15	1	17	1	19	
t _{PHZ}	OE	Q _A - Q _H			8.1	15.7	1	16.2	1	18.2	
t _{PLZ}					9.3	15.7	1	16.2	1	18.2	

6.11 Switching Characteristics, $V_{CC} = 5\text{ V} \pm 0.5\text{ V}$

over recommended operating free-air temperature range (unless otherwise noted) (see 图 7-1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	LOAD CAPACITANCE	T _A = 25°C			– 40°C to 85°C		– 40°C to 125°C		UNIT
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
f _{max}			C _L = 15 pF	135	170		115		115		MHz
			C _L = 50 pF	120	140		95		95		
t _{PLH}	RCLK	Q _A – Q _H	C _L = 15 pF		4.3	7.4	1	8.5	1	9.5	ns
t _{PHL}					4.3	7.4	1	8.5	1	9.5	
t _{PLH}	SRCLK	Q _H '			4.5	8.2	1	9.4	1	10.4	
t _{PHL}					4.5	8.2	1	9.4	1	10.4	
t _{PHL}	SRCLR	Q _H '			4.5	8	1	9.1	1	10.1	
t _{PZH}	OE	Q _A – Q _H			4.3	8.6	1	10	1	11	
t _{PZL}					5.4	8.6	1	10	1	11	
t _{PHZ}	OE	Q _A – Q _H			2.4	6	1	7.1	1	7.1	
t _{PLZ}					2.7	5.1	1	7.2	1	7.2	
t _{PLH}	RCLK	Q _A – Q _H		C _L = 50 pF		5.6	9.4	1	10.5	1	
t _{PHL}					5.6	9.4	1	10.5	1	12.5	
t _{PLH}	SRCLK	Q _H '			6.4	10.2	1	11.4	1	13.4	
t _{PHL}					6.4	10.2	1	11.4	1	13.4	
t _{PHL}	SRCLR	Q _H '			6.4	10	1	11.1	1	13.1	
t _{PZH}	OE	Q _A – Q _H			5.7	10.6	1	12	1	14	
t _{PZL}					6.8	10.6	1	12	1	14	
t _{PHZ}	OE	Q _A – Q _H			3.5	10.3	1	11	1	13	
t _{PLZ}					3.4	10.3	1	11	1	13	

6.12 Noise Characteristics

$V_{CC} = 3.3\text{ V}$, $C_L = 50\text{ pF}$, $T_A = 25^\circ\text{C}$ ⁽¹⁾

PARAMETER		MIN	TYP	MAX	UNIT
$V_{OL(P)}$	Quiet output, maximum dynamic V_{OL}		0.3		V
$V_{OL(V)}$	Quiet output, minimum dynamic V_{OL}		-0.2		V
$V_{OH(V)}$	Quiet output, minimum dynamic V_{OH}		2.8		V
$V_{IH(D)}$	High-level dynamic input voltage	2.31			V
$V_{IL(D)}$	Low-level dynamic input voltage			0.99	V

(1) Characteristics are for surface-mount packages only.

6.13 Operating Characteristics

$T_A = 25^\circ\text{C}$

PARAMETER		TEST CONDITIONS		V_{CC}	TYP	UNIT
C_{pd}	Power dissipation capacitance	$C_L = 50\text{ pF}$, $f = 10\text{ MHz}$		3.3 V	111	pF
				5 V	114	

6.14 Typical Characteristics

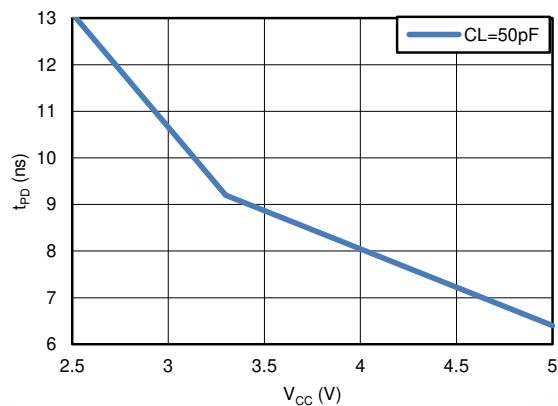
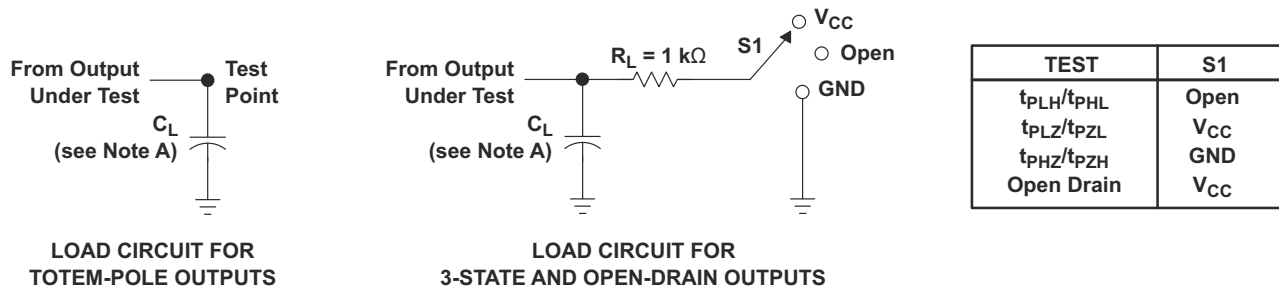


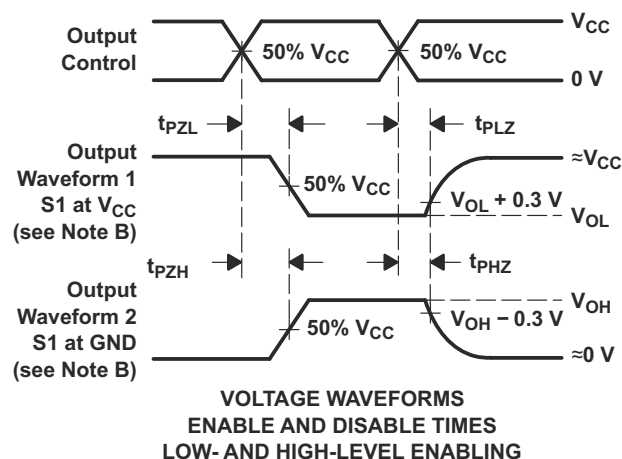
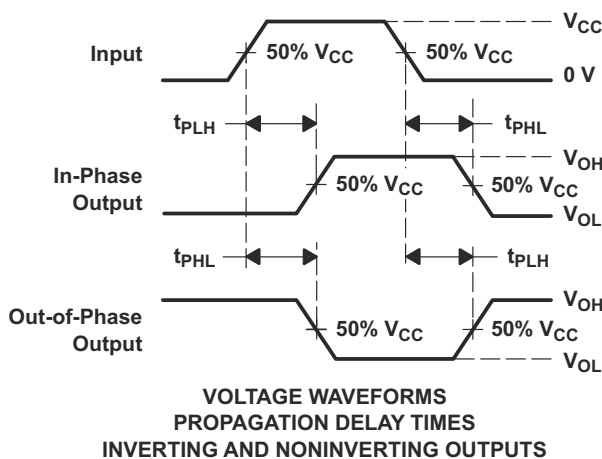
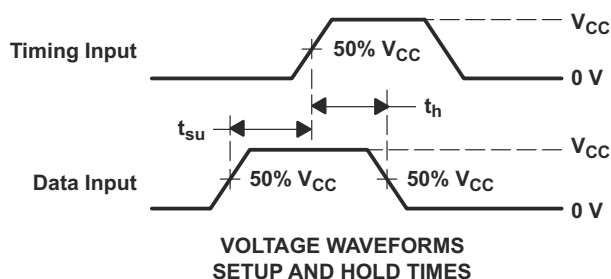
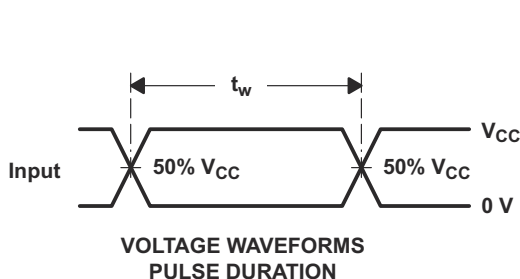
图 6-1. TPD vs V_{CC}

7 Parameter Measurement Information



LOAD CIRCUIT FOR
TOTEM-POLE OUTPUTS

LOAD CIRCUIT FOR
3-STATE AND OPEN-DRAIN OUTPUTS



- A. C_L includes probe and jig capacitance.
- B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: $PRR \leq 1\text{ MHz}$, $Z_O = 50\ \Omega$, $t_r \leq 3\text{ ns}$, $t_f \leq 3\text{ ns}$.
- D. The outputs are measured one at a time, with one input transition per measurement.
- E. t_{PLZ} and t_{PHZ} are the same as t_{dis} .
- F. t_{PZL} and t_{PZH} are the same as t_{en} .
- G. t_{PHL} and t_{PLH} are the same as t_{pd} .
- H. All parameters and waveforms are not applicable to all devices.

图 7-1. Load Circuit and Voltage Waveforms

8 Detailed Description

8.1 Overview

The SN74LV595A device contains an 8-bit serial-in, parallel-out shift register that feeds an 8-bit D-type storage register. The storage register has parallel 3-state outputs. Separate clocks are provided for the shift and storage registers. The shift register has a direct overriding clear ($\overline{\text{SRCLR}}$) input, serial (SER) input, and serial outputs for cascading. When the output-enable ($\overline{\text{OE}}$) input is high, the outputs are in the high-impedance state. Both the shift register clock (SRCLK) and storage register clock (RCLK) are positive-edge triggered. If both clocks are connected together, then the shift register always is one clock pulse ahead of the storage register.

8.2 Functional Block Diagram

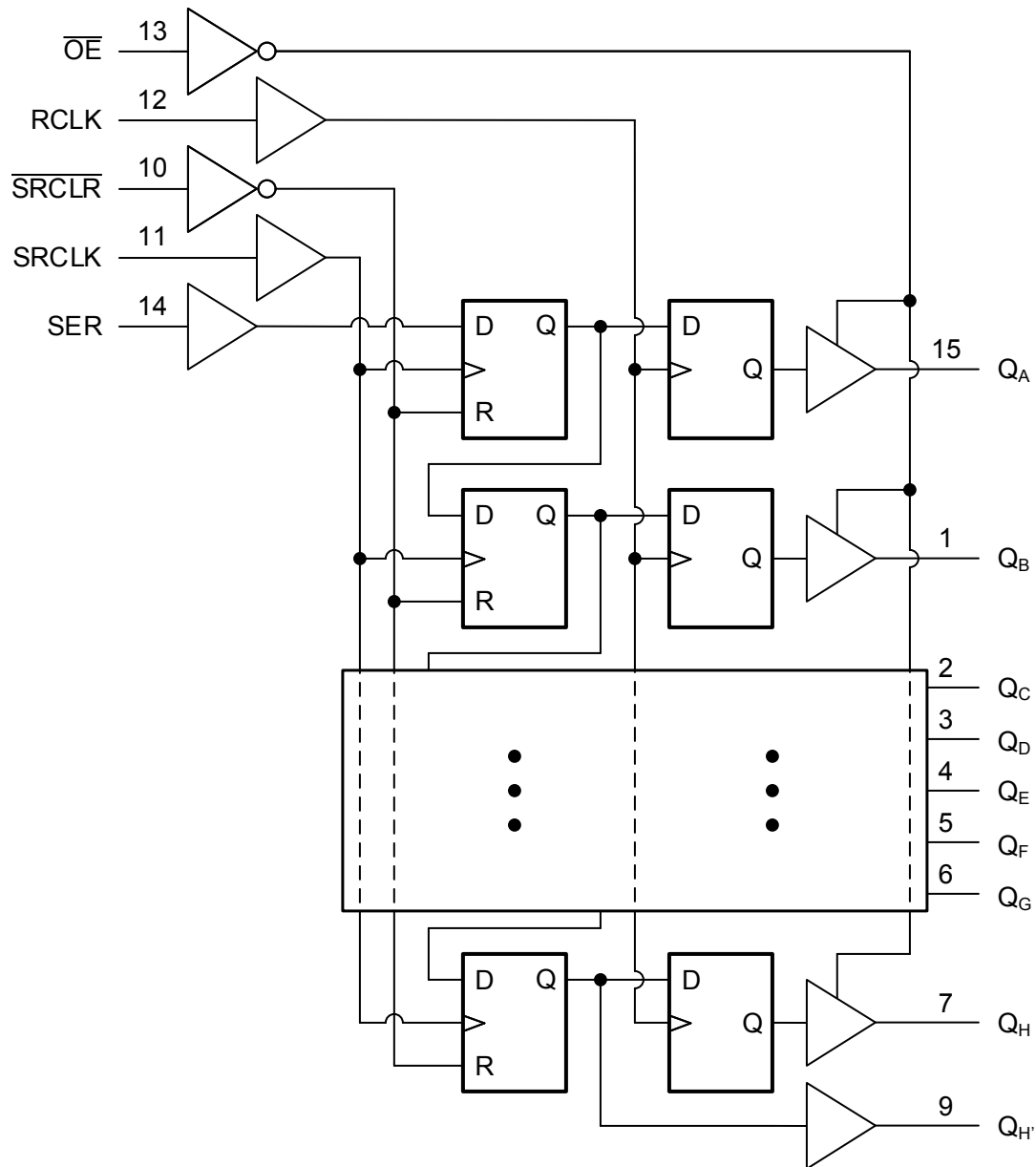


图 8-1. Logic Diagram (Positive Logic)

8.3 Feature Description

8.3.1 Balanced CMOS 3-State Outputs

This device includes balanced CMOS 3-state outputs. Driving high, driving low, and high impedance are the three states that these outputs can be in. The term *balanced* indicates that the device can sink and source similar currents. The drive capability of this device may create fast edges into light loads, so routing and load conditions should be considered to prevent ringing. Additionally, the outputs of this device can drive larger currents than the device can sustain without being damaged. It is important for the output power of the device to be limited to avoid damage due to overcurrent. The electrical and thermal limits defined in the *Absolute Maximum Ratings* must be followed at all times.

When placed into the high-impedance mode, the output will neither source nor sink current, with the exception of minor leakage current as defined in the *Electrical Characteristics* table. In the high-impedance state, the output voltage is not controlled by the device and is dependent on external factors. If no other drivers are connected to the node, then this is known as a floating node and the voltage is unknown. A pull-up or pull-down resistor can be connected to the output to provide a known voltage at the output while it is in the high-impedance state. The value of the resistor will depend on multiple factors, including parasitic capacitance and power consumption limitations. Typically, a 10-k Ω resistor can be used to meet these requirements.

Unused 3-state CMOS outputs should be left disconnected.

8.3.2 Latching Logic

This device includes latching logic circuitry. Latching circuits commonly include D-type latches and D-type flip-flops, but include all logic circuits that act as volatile memory.

When the device is powered on, the state of each latch is unknown. There is no default state for each latch at start-up.

The output state of each latching logic circuit only remains stable as long as power is applied to the device within the supply voltage range specified in the *Recommended Operating Conditions* table.

8.3.3 Partial Power Down (I_{off})

This device includes circuitry to disable all outputs when the supply pin is held at 0 V. When disabled, the outputs will neither source nor sink current, regardless of the input voltages applied. The amount of leakage current at each output is defined by the I_{off} specification in the *Electrical Characteristics* table.

8.3.4 Clamp Diode Structure

图 8-2 shows the inputs and outputs to this device have negative clamping diodes only.

CAUTION

Voltages beyond the values specified in the *Absolute Maximum Ratings* table can cause damage to the device. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

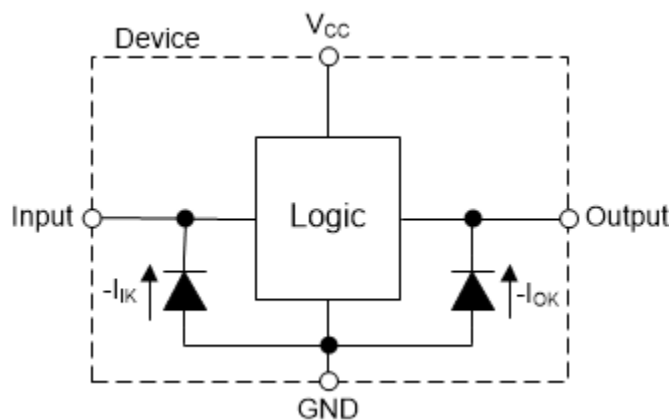


图 8-2. Electrical Placement of Clamping Diodes for Each Input and Output

8.4 Device Functional Modes

表 8-1. Function Table

INPUTS ⁽¹⁾					FUNCTION
SER	SRCLK	SRCLR	RCLK	OE	
X	X	X	X	H	Outputs Q _A –Q _H are disabled. Q _H Remains enabled.

表 8-1. Function Table (continued)

INPUTS ⁽¹⁾					FUNCTION
SER	SRCLK	SRCLR	RCLK	OE	
X	X	X	X	L	Outputs Q _A –Q _H are enabled.
X	X	L	X	X	Shift register is cleared.
L	↑	H	X	X	First stage of the shift register goes low. Other stages store the data of previous stage, respectively.
H	↑	H	X	X	First stage of the shift register goes high. Other stages store the data of previous stage, respectively.
X	X	X	↑	X	Shift-register data is stored in the storage register.

(1) H = High Voltage Level, L = Low Voltage Level, X = Do not Care, Z = High Impedance

9 Application and Implementation

备注

以下应用部分中的信息不属于 TI 器件规格的范围，TI 不担保其准确性和完整性。TI 的客户应负责确定器件是否适用于其应用。客户应验证并测试其设计，以确保系统功能。

9.1 Application Information

The SN74LV595A is a low-drive CMOS device that can be used for a multitude of bus interface type applications where output ringing is a concern. The low drive and slow edge rates will minimize overshoot and undershoot on the outputs. The inputs are 5-V tolerant allowing for down translation to V_{CC} .

9.2 Typical Application

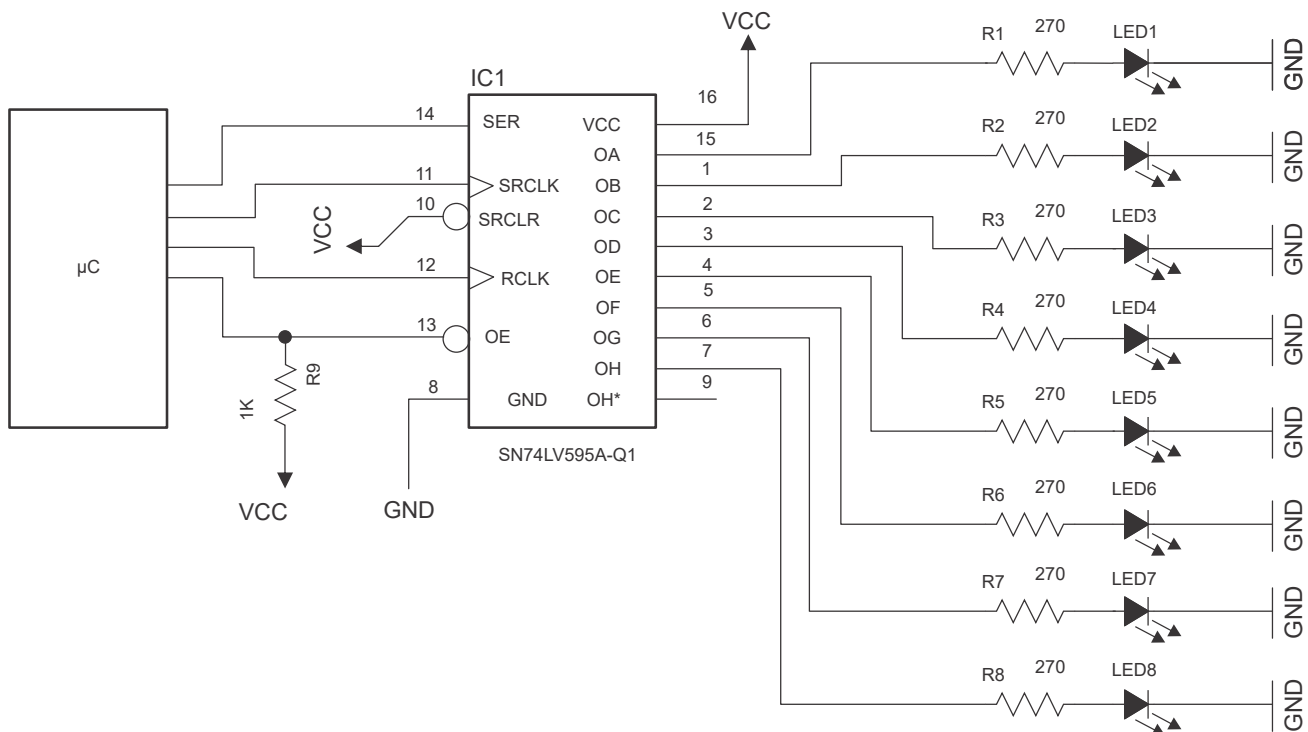


图 9-1. SN74LV595A Expanding IOs to Drive LEDs

9.2.1 Power Considerations

Ensure the desired supply voltage is within the range specified in the *Recommended Operating Conditions*. The supply voltage sets the device's electrical characteristics as described in the *Electrical Characteristics* section.

The positive voltage supply must be capable of sourcing current equal to the total current to be sourced by all outputs of the SN74LV595A plus the maximum static supply current, I_{CC} , listed in the *Electrical Characteristics*, and any transient current required for switching. The logic device can only source as much current that is provided by the positive supply source. Be sure to not exceed the maximum total current through V_{CC} listed in the *Absolute Maximum Ratings*.

The ground must be capable of sinking current equal to the total current to be sunk by all outputs of the SN74LV595A plus the maximum supply current, I_{CC} , listed in the *Electrical Characteristics*, and any transient

current required for switching. The logic device can only sink as much current that can be sunk into its ground connection. Be sure to not exceed the maximum total current through GND listed in the *Absolute Maximum Ratings*.

The SN74LV595A can drive a load with a total capacitance less than or equal to 50 pF while still meeting all of the data sheet specifications. Larger capacitive loads can be applied; however, it is not recommended to exceed 50 pF.

The SN74LV595A can drive a load with total resistance described by $R_L \geq V_O / I_O$, with the output voltage and current defined in the *Electrical Characteristics* table with V_{OH} and V_{OL} . When outputting in the HIGH state, the output voltage in the equation is defined as the difference between the measured output voltage and the supply voltage at the V_{CC} pin.

Total power consumption can be calculated using the information provided in [CMOS Power Consumption and Cpd Calculation](#).

Thermal increase can be calculated using the information provided in [Thermal Characteristics of Standard Linear and Logic \(SLL\) Packages and Devices](#).

CAUTION

The maximum junction temperature, $T_{J(max)}$ listed in the *Absolute Maximum Ratings*, is an additional limitation to prevent damage to the device. Do not violate any values listed in the *Absolute Maximum Ratings*. These limits are provided to prevent damage to the device.

9.2.2 Input Considerations

Input signals must cross $V_{IL(max)}$ to be considered a logic LOW, and $V_{IH(min)}$ to be considered a logic HIGH. Do not exceed the maximum input voltage range found in the *Absolute Maximum Ratings*.

Unused inputs must be terminated to either V_{CC} or ground. The unused inputs can be directly terminated if the input is completely unused, or they can be connected with a pull-up or pull-down resistor if the input will be used sometimes, but not always. A pull-up resistor is used for a default state of HIGH, and a pull-down resistor is used for a default state of LOW. The drive current of the controller, leakage current into the SN74LV595A (as specified in the *Electrical Characteristics*), and the desired input transition rate limits the resistor size. A 10-k Ω resistor value is often used due to these factors.

The SN74LV595A has CMOS inputs and thus requires fast input transitions to operate correctly, as defined in the *Recommended Operating Conditions* table. Slow input transitions can cause oscillations, additional power consumption, and reduction in device reliability.

Refer to the *Feature Description* section for additional information regarding the inputs for this device.

9.2.3 Output Considerations

The positive supply voltage is used to produce the output HIGH voltage. Drawing current from the output will decrease the output voltage as specified by the V_{OH} specification in the *Electrical Characteristics*. The ground voltage is used to produce the output LOW voltage. Sinking current into the output will increase the output voltage as specified by the V_{OL} specification in the *Electrical Characteristics*.

Push-pull outputs that could be in opposite states, even for a very short time period, should never be connected directly together. This can cause excessive current and damage to the device.

Two channels within the same device with the same input signals can be connected in parallel for additional output drive strength.

Unused outputs can be left floating. Do not connect outputs directly to V_{CC} or ground.

Refer to the *Feature Description* section for additional information regarding the outputs for this device.

9.2.4 Design Requirements

This device uses CMOS technology and has balanced output drive. Care should be taken to avoid bus contention because it can drive currents that would exceed maximum limits. The high drive will also create fast edges into light loads so routing and load conditions should be considered to prevent ringing.

9.2.5 Detailed Design Procedure

1. Add a decoupling capacitor from V_{CC} to GND. The capacitor needs to be placed physically close to the device and electrically close to both the V_{CC} and GND pins. An example layout is shown in the *Layout* section.
2. Ensure the capacitive load at the output is ≤ 50 pF. This is not a hard limit; it will, however, ensure optimal performance. This can be accomplished by providing short, appropriately sized traces from the SN74LV595A to one or more of the receiving devices.
3. Ensure the resistive load at the output is larger than $(V_{CC} / I_{O(max)}) \Omega$. This will ensure that the maximum output current from the *Absolute Maximum Ratings* is not violated. Most CMOS inputs have a resistive load measured in $M\Omega$; much larger than the minimum calculated previously.
4. Thermal issues are rarely a concern for logic gates; the power consumption and thermal increase, however, can be calculated using the steps provided in the application report, [CMOS Power Consumption and Cpd Calculation](#).

9.2.6 Application Curves

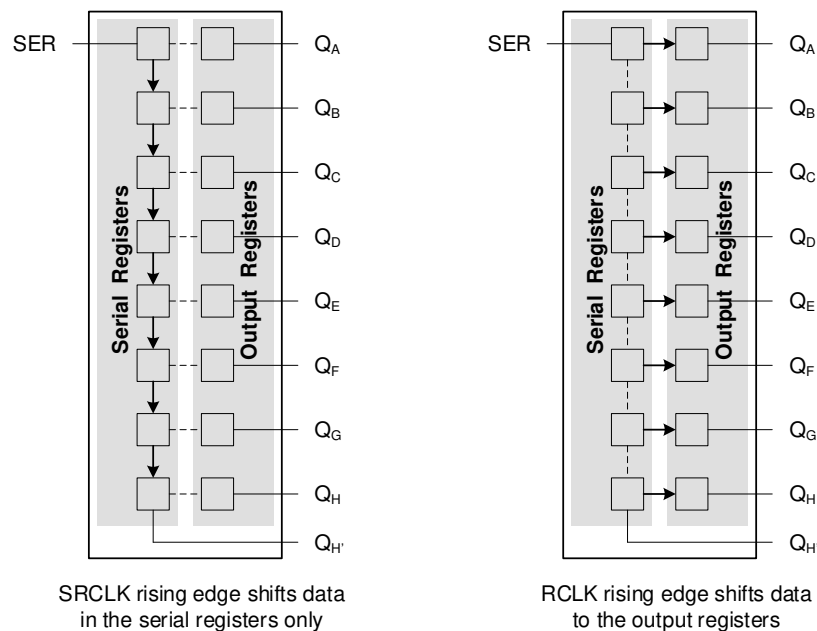


图 9-2. Simplified Functional Diagram Showing Clock Operation

9.3 Power Supply Recommendations

The power supply can be any voltage between the MIN and MAX supply voltage rating located in the [Recommended Operating Conditions](#) table.

Each V_{CC} terminal should have a good bypass capacitor to prevent power disturbance. For devices with a single supply, a $0.1 \mu F$ capacitor is recommended. If there are multiple V_{CC} terminals then $0.01 \mu F$ or $0.022 \mu F$ capacitors are recommended for each power terminal. It is ok to parallel multiple bypass capacitors to reject different frequencies of noise. $0.1 \mu F$ and $1.0 \mu F$ capacitors are commonly used in parallel. The bypass capacitor should be installed as close to the power terminal as possible for the best results.

9.4 Layout

9.4.1 Layout Guidelines

When using multiple bit logic devices, inputs should not float. In many cases, functions or parts of functions of digital logic devices are unused. Some examples are when only two inputs of a triple-input AND gate are used, or when only 3 of the 4-buffer gates are used. Such unused input pins must not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. All unused inputs of digital logic devices must be connected to a logic high or logic low voltage, as defined by the input voltage specifications, to prevent them from floating. The logic level that must be applied to any particular unused input depends on the function of the device. Generally, the inputs are tied to GND or VCC, whichever makes more sense for the logic function or is more convenient.

9.4.2 Layout Example

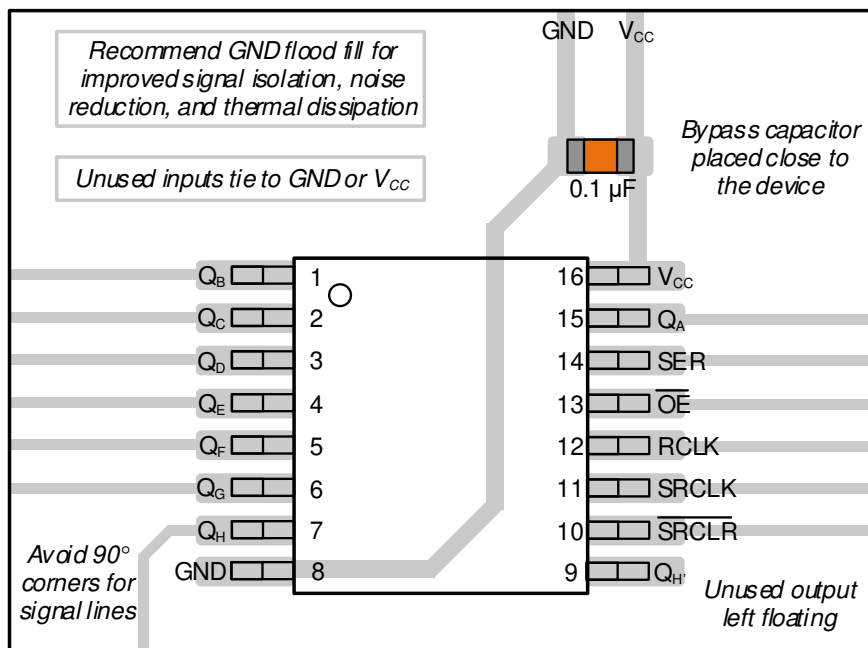


图 9-3. Layout Example for the SN74LV595A in TSSOP

10 Device and Documentation Support

10.1 Documentation Support

10.1.1 Related Documentation

For related documentation, see the following:

- Texas Instruments, [CMOS Power Consumption and Cpd Calculation application report](#)
- Texas Instruments, [Thermal Characteristics of Standard Linear and Logic \(SLL\) Packages and Devices application report](#)

10.2 接收文档更新通知

要接收文档更新通知，请导航至 [ti.com](https://www.ti.com) 上的器件产品文件夹。点击 [订阅更新](#) 进行注册，即可每周接收产品信息更改摘要。有关更改的详细信息，请查看任何已修订文档中包含的修订历史记录。

10.3 支持资源

TI E2E™ [支持论坛](#) 是工程师的重要参考资料，可直接从专家获得快速、经过验证的解答和设计帮助。搜索现有解答或提出自己的问题可获得所需的快速设计帮助。

链接的内容由各个贡献者“按原样”提供。这些内容并不构成 TI 技术规范，并且不一定反映 TI 的观点；请参阅 TI 的《[使用条款](#)》。

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ESD 的损坏小至导致微小的性能降级，大至整个器件故障。精密的集成电路可能更容易受到损坏，这是因为非常细微的参数更改都可能会导致器件与其发布的规格不相符。

10.6 术语表

[TI 术语表](#) 本术语表列出并解释了术语、首字母缩略词和定义。

11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
SN74LV595ABQBR	ACTIVE	WQFN	BQB	16	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LV595A	Samples
SN74LV595AD	OBSOLETE	SOIC	D	16		TBD	Call TI	Call TI	-40 to 125	LV595A	
SN74LV595ADR	ACTIVE	SOIC	D	16	2500	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	LV595A	Samples
SN74LV595ADRG3	ACTIVE	SOIC	D	16	2500	RoHS & Green	SN	Level-1-260C-UNLIM	-40 to 125	LV595A	Samples
SN74LV595ADRG4	ACTIVE	SOIC	D	16	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LV595A	Samples
SN74LV595ANSR	ACTIVE	SO	NS	16	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	74LV595A	Samples
SN74LV595APWR	ACTIVE	TSSOP	PW	16	2000	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	LV595A	Samples
SN74LV595APWRG3	ACTIVE	TSSOP	PW	16	2000	RoHS & Green	SN	Level-1-260C-UNLIM	-40 to 125	LV595A	Samples
SN74LV595APWRG4	ACTIVE	TSSOP	PW	16	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LV595A	Samples
SN74LV595APWT	OBSOLETE	TSSOP	PW	16		TBD	Call TI	Call TI	-40 to 125	LV595A	
SN74LV595ARGYR	ACTIVE	VQFN	RGY	16	3000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	LV595A	Samples
SN74LV595ARGYRG4	ACTIVE	VQFN	RGY	16	3000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	LV595A	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

⁽⁵⁾ Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

⁽⁶⁾ Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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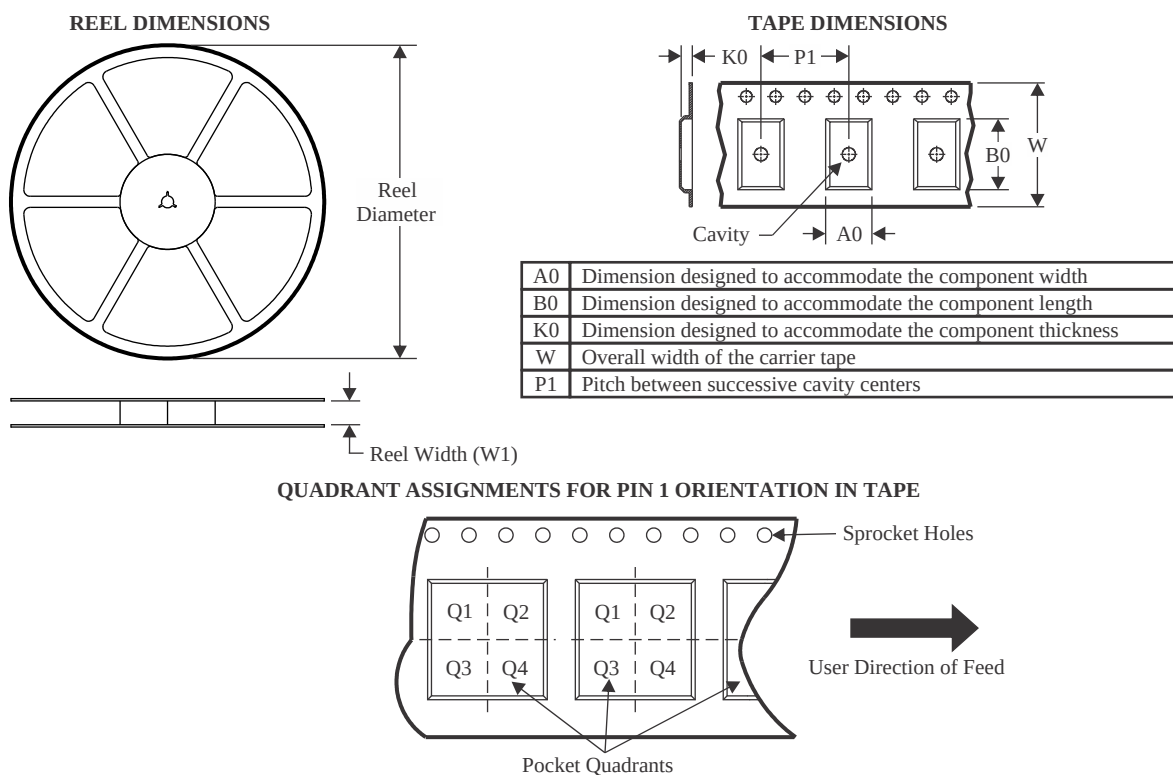
OTHER QUALIFIED VERSIONS OF SN74LV595A :

- Automotive : [SN74LV595A-Q1](#)
- Enhanced Product : [SN74LV595A-EP](#)

NOTE: Qualified Version Definitions:

- Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects
- Enhanced Product - Supports Defense, Aerospace and Medical Applications

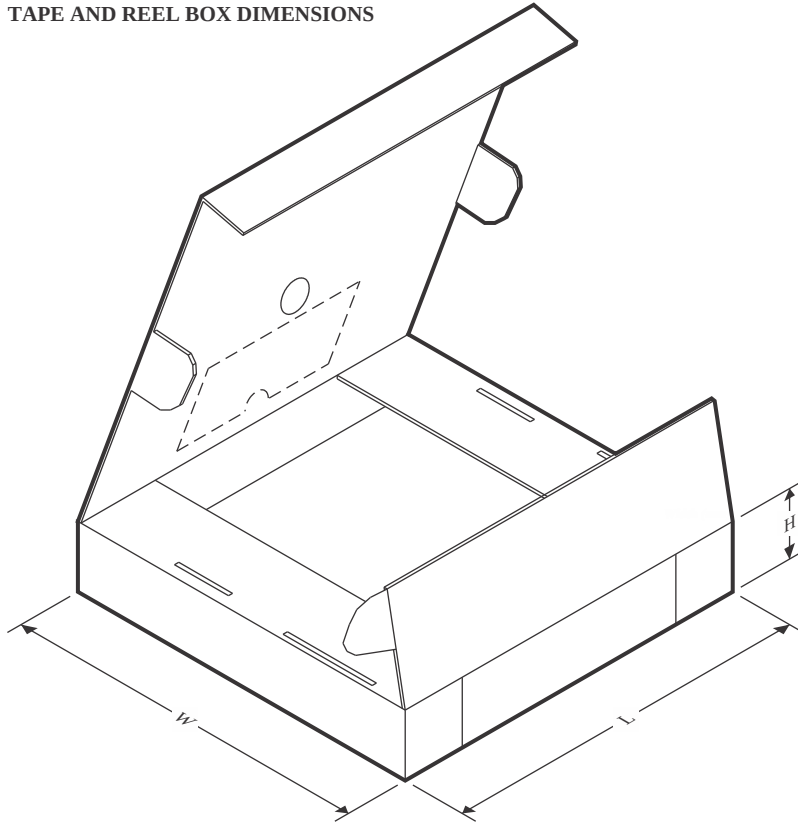
TAPE AND REEL INFORMATION



*All dimensions are nominal

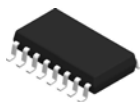
Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74LV595ABQBR	WQFN	BQB	16	3000	180.0	12.4	2.8	3.8	1.2	4.0	12.0	Q1
SN74LV595ADR	SOIC	D	16	2500	330.0	12.4	3.75	3.75	1.15	8.0	12.0	Q1
SN74LV595ADR	SOIC	D	16	2500	330.0	16.4	6.5	10.3	2.1	8.0	16.0	Q1
SN74LV595ADRG3	SOIC	D	16	2500	330.0	16.8	6.5	10.3	2.1	8.0	16.0	Q1
SN74LV595ADRG4	SOIC	D	16	2500	330.0	16.4	6.5	10.3	2.1	8.0	16.0	Q1
SN74LV595ANSR	SO	NS	16	2000	330.0	16.4	8.2	10.5	2.5	12.0	16.0	Q1
SN74LV595APWR	TSSOP	PW	16	2000	330.0	12.4	6.85	5.45	1.6	8.0	12.0	Q1
SN74LV595APWR	TSSOP	PW	16	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
SN74LV595APWR	TSSOP	PW	16	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
SN74LV595APWRG3	TSSOP	PW	16	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
SN74LV595APWRG4	TSSOP	PW	16	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
SN74LV595APWRG4	TSSOP	PW	16	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
SN74LV595ARGYR	VQFN	RGY	16	3000	330.0	12.4	3.8	4.3	1.5	8.0	12.0	Q1

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74LV595ABQBR	WQFN	BQB	16	3000	210.0	185.0	35.0
SN74LV595ADR	SOIC	D	16	2500	340.5	336.1	32.0
SN74LV595ADR	SOIC	D	16	2500	340.5	336.1	32.0
SN74LV595ADRG3	SOIC	D	16	2500	364.0	364.0	27.0
SN74LV595ADRG4	SOIC	D	16	2500	340.5	336.1	32.0
SN74LV595ANSR	SO	NS	16	2000	356.0	356.0	35.0
SN74LV595APWR	TSSOP	PW	16	2000	366.0	364.0	50.0
SN74LV595APWR	TSSOP	PW	16	2000	353.0	353.0	32.0
SN74LV595APWR	TSSOP	PW	16	2000	356.0	356.0	35.0
SN74LV595APWRG3	TSSOP	PW	16	2000	364.0	364.0	27.0
SN74LV595APWRG4	TSSOP	PW	16	2000	353.0	353.0	32.0
SN74LV595APWRG4	TSSOP	PW	16	2000	356.0	356.0	35.0
SN74LV595ARGYR	VQFN	RGY	16	3000	356.0	356.0	35.0

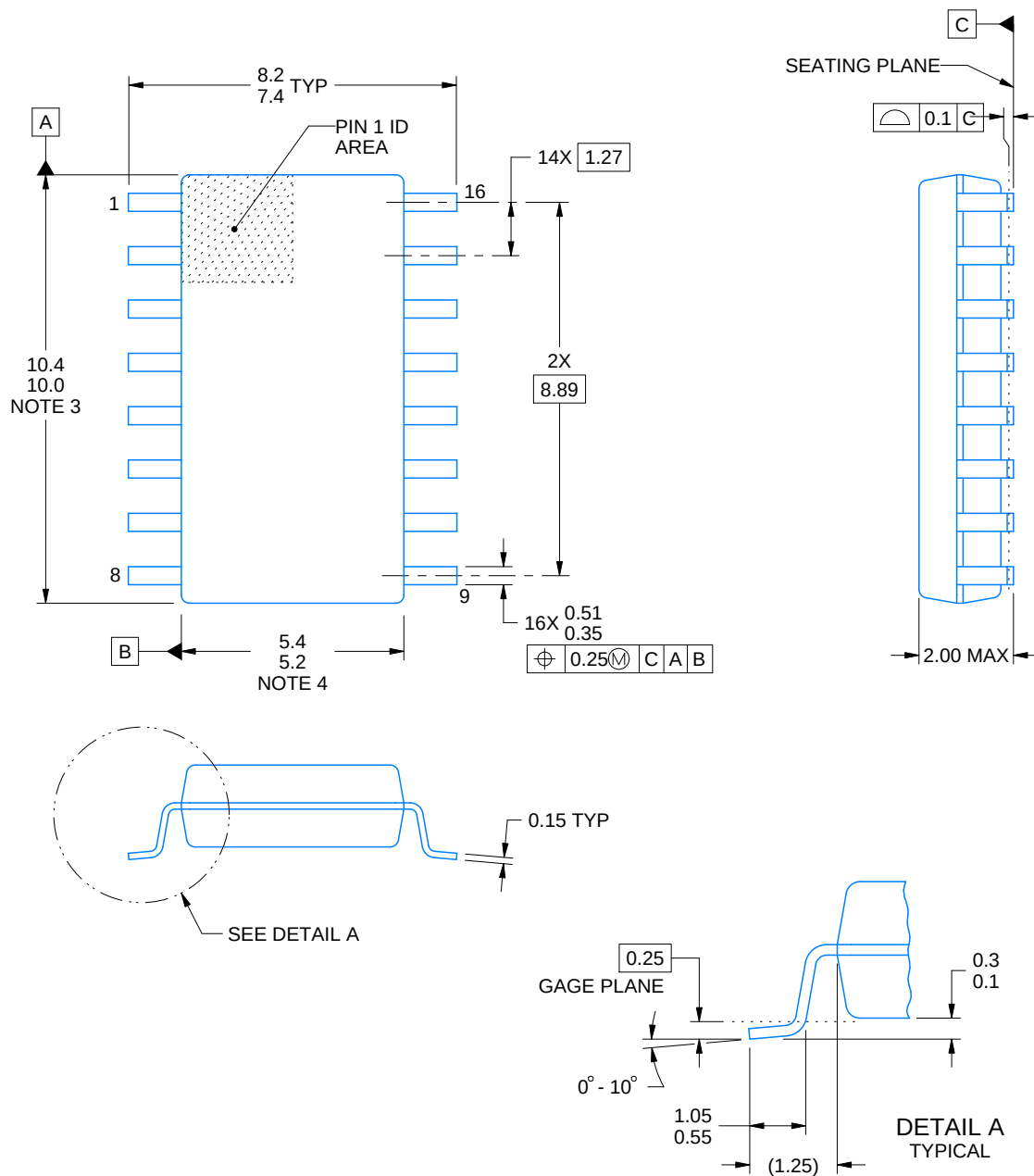


PACKAGE OUTLINE

NS0016A

SOP - 2.00 mm max height

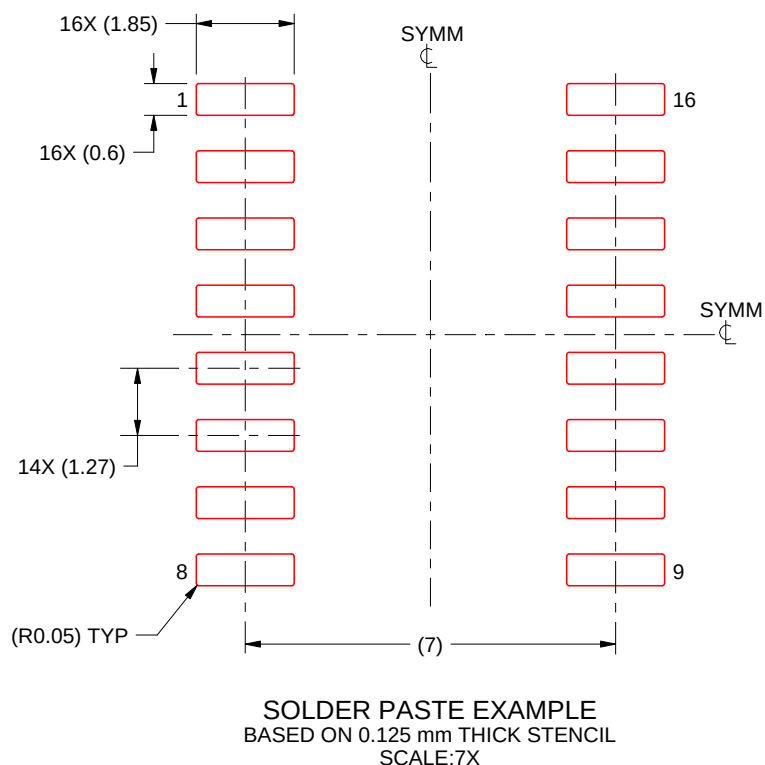
SOP



4220735/A 12/2021

NOTES:

1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm, per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm, per side.



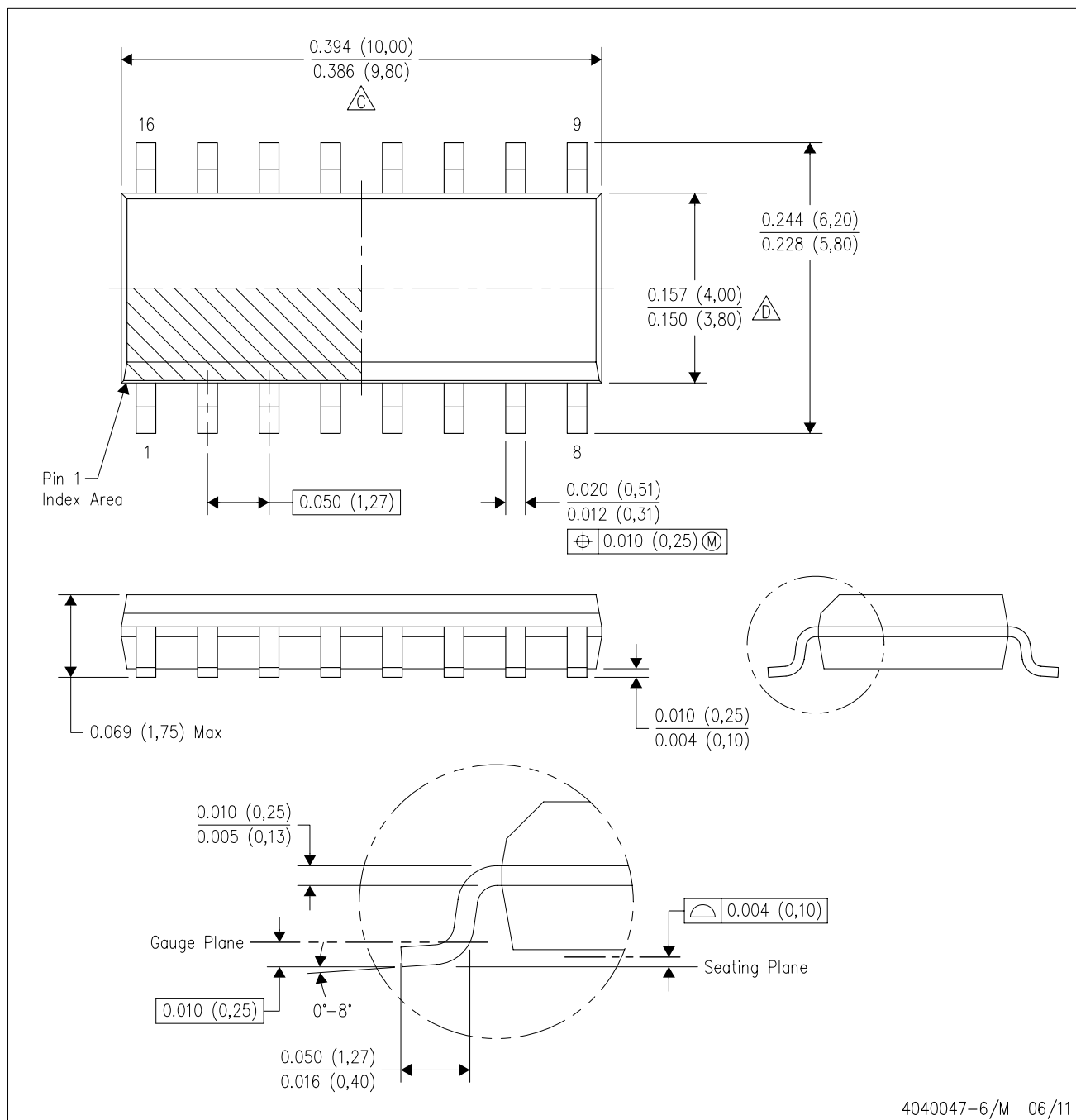
4220735/A 12/2021

NOTES: (continued)

7. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
8. Board assembly site may have different recommendations for stencil design.

D (R-PDSO-G16)

PLASTIC SMALL OUTLINE



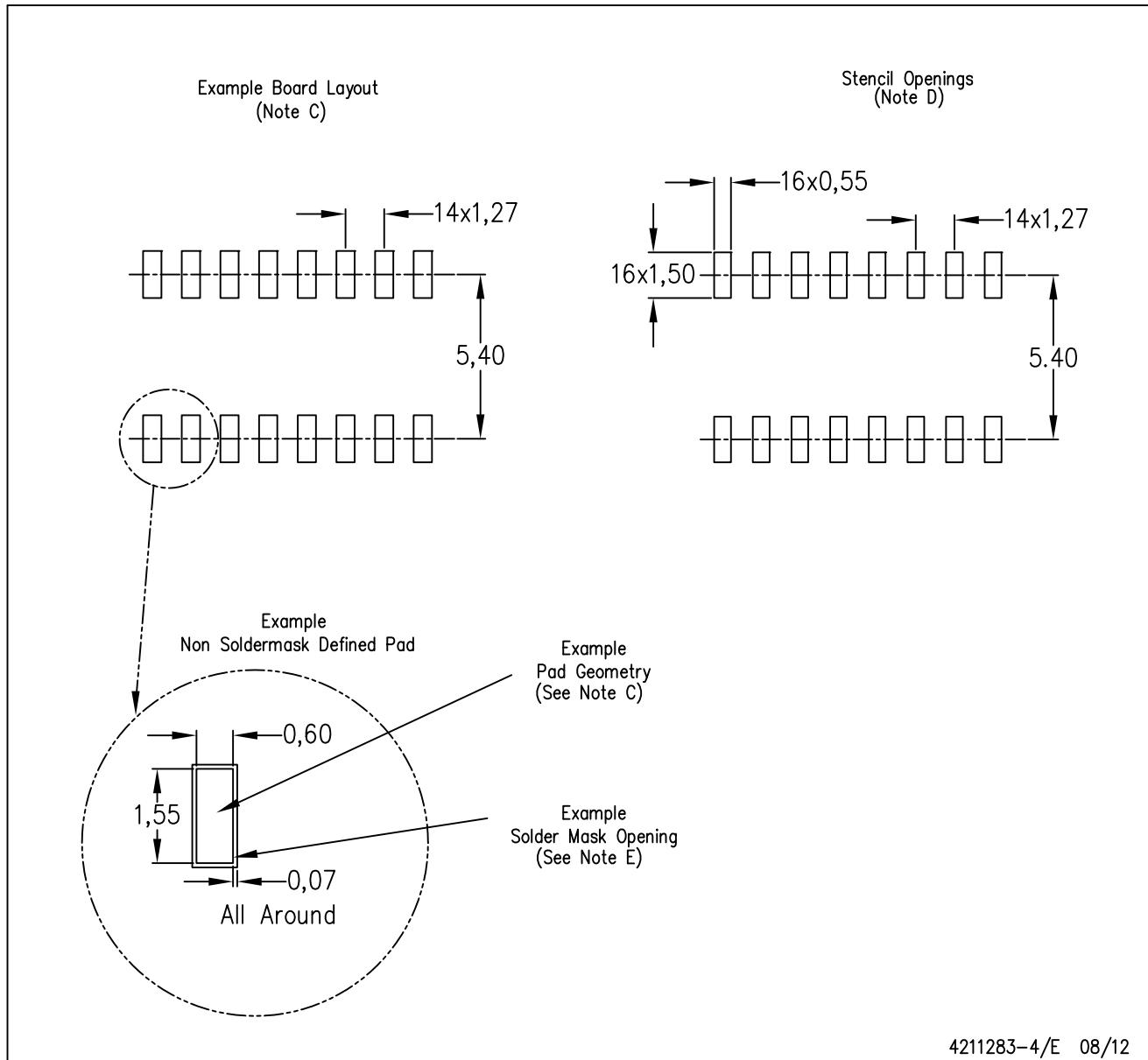
4040047-6/M 06/11

NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- $\triangle C$ Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
- $\triangle D$ Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
- E. Reference JEDEC MS-012 variation AC.

D (R-PDSO-G16)

PLASTIC SMALL OUTLINE



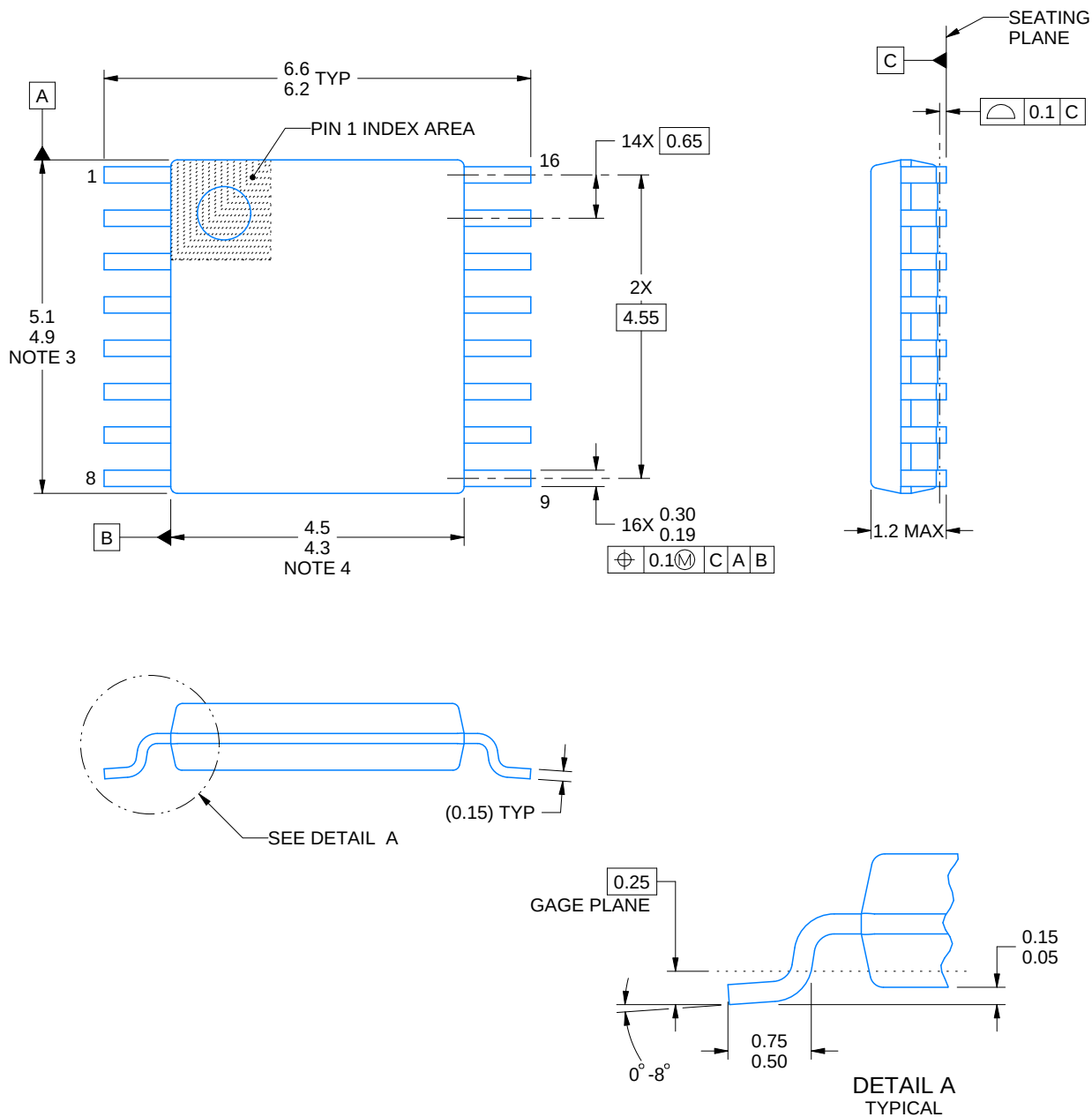
- NOTES:
- All linear dimensions are in millimeters.
 - This drawing is subject to change without notice.
 - Publication IPC-7351 is recommended for alternate designs.
 - Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
 - Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



PW0016A

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



4220204/A 02/2017

NOTES:

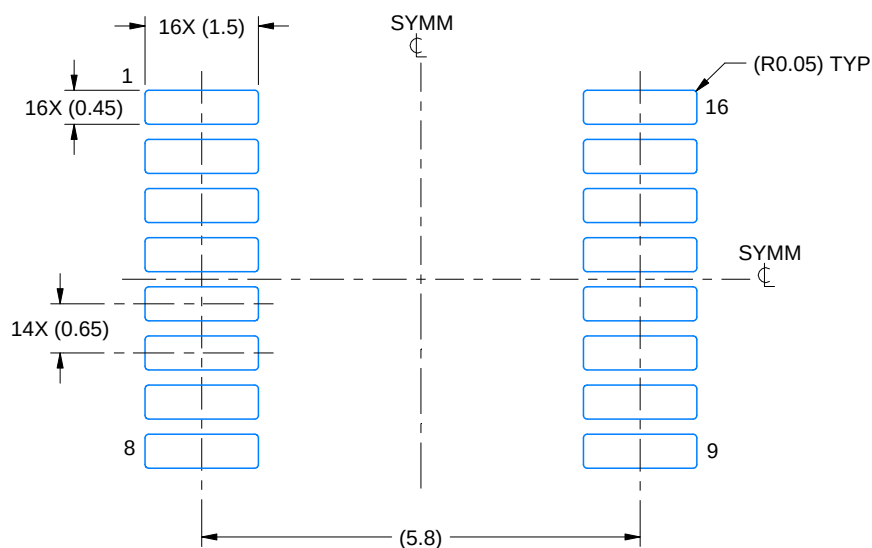
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
5. Reference JEDEC registration MO-153.

EXAMPLE BOARD LAYOUT

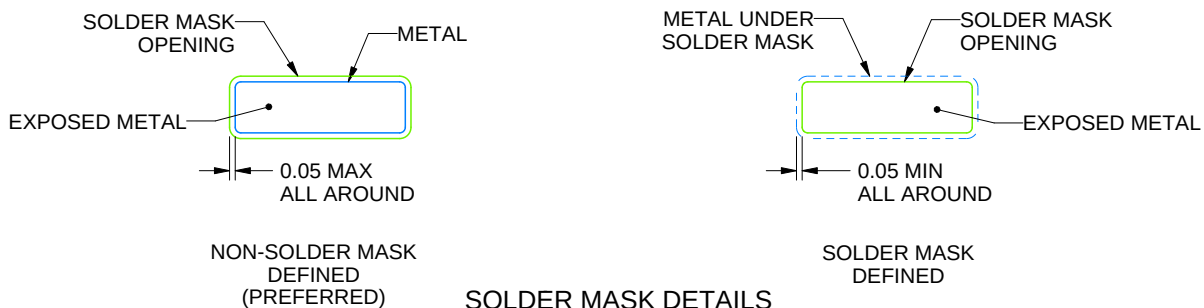
PW0016A

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 10X



4220204/A 02/2017

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

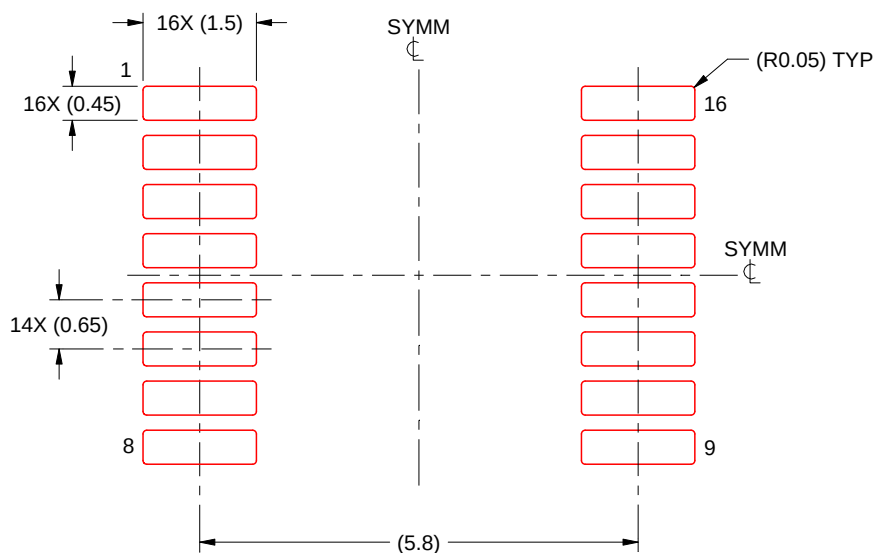
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

PW0016A

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



4220204/A 02/2017

NOTES: (continued)

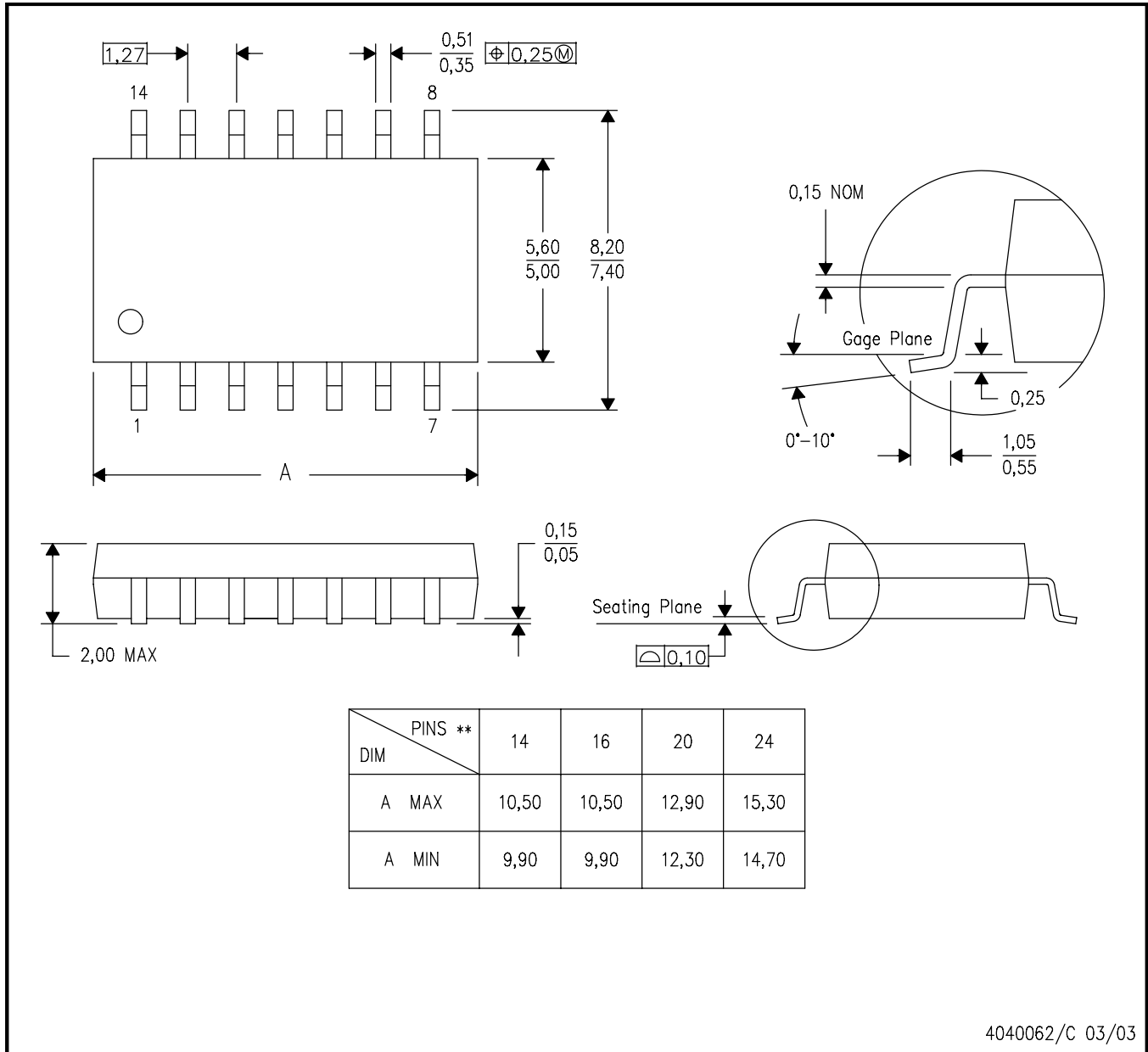
8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

MECHANICAL DATA

NS (R-PDSO-G**)

PLASTIC SMALL-OUTLINE PACKAGE

14-PINS SHOWN



- NOTES:
- A. All linear dimensions are in millimeters.
 - B. This drawing is subject to change without notice.
 - C. Body dimensions do not include mold flash or protrusion, not to exceed 0,15.

GENERIC PACKAGE VIEW

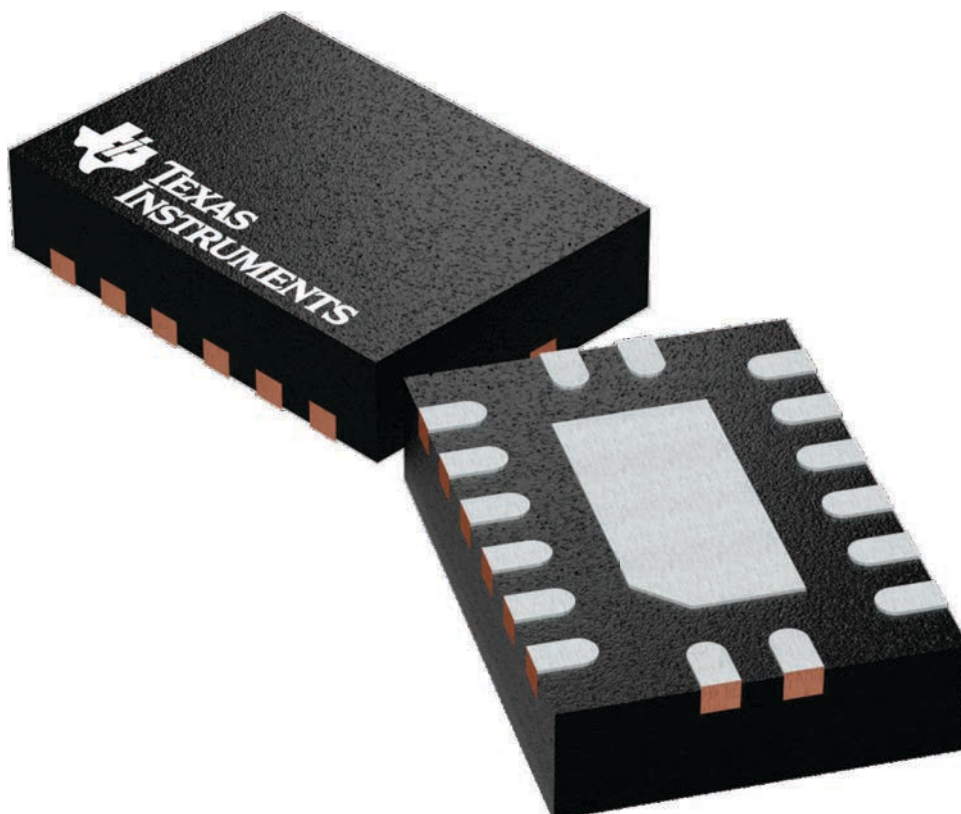
BQB 16

WQFN - 0.8 mm max height

2.5 x 3.5, 0.5 mm pitch

PLASTIC QUAD FLATPACK - NO LEAD

This image is a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.

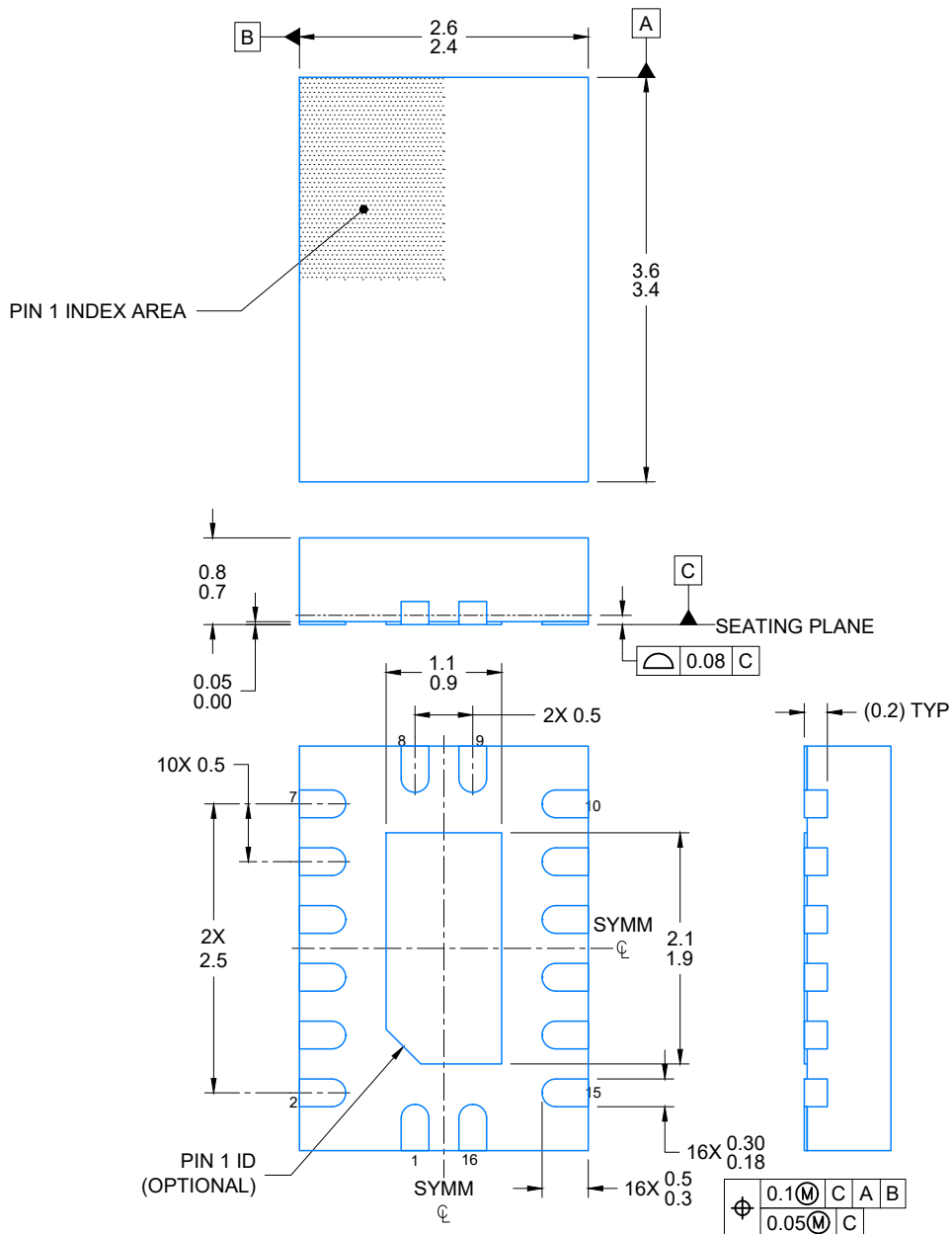


4226161/A

PACKAGE OUTLINE

WQFN - 0.8 mm max height

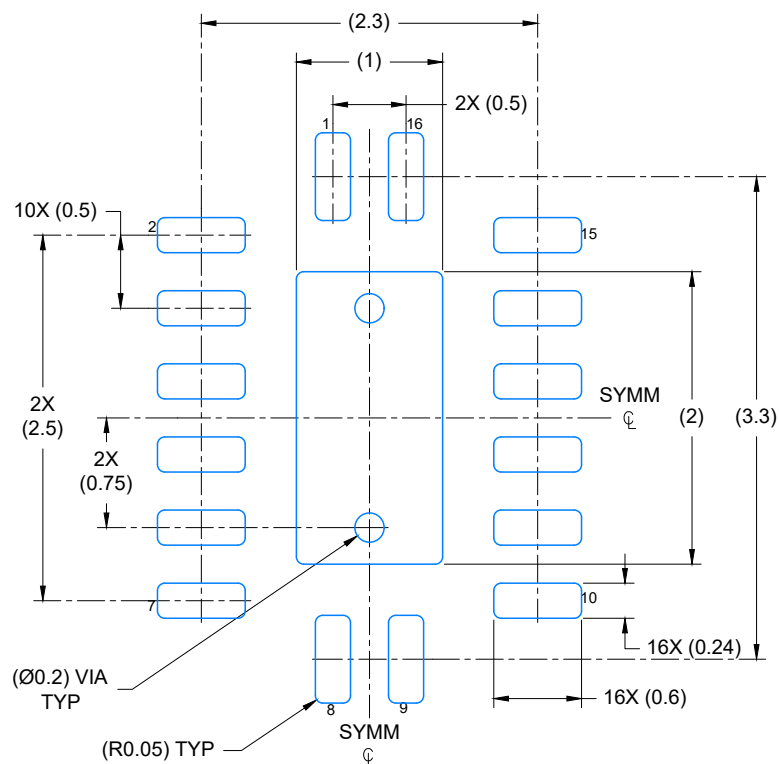
PLASTIC QUAD FLAT PACK-NO LEAD



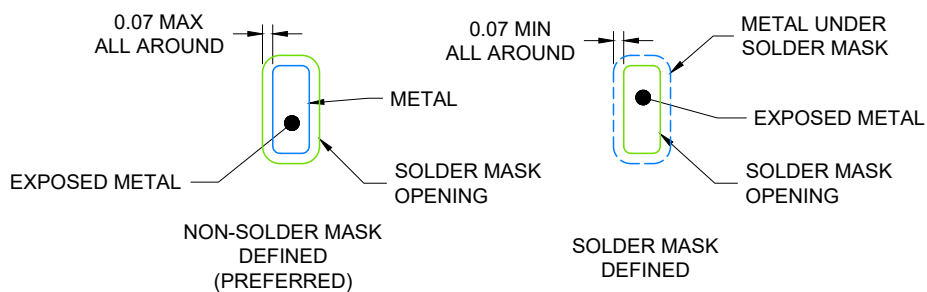
4224640/A 11/2018

NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. The package thermal pad must be soldered to the printed circuit board for optimal thermal and mechanical performance.



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 20X



4224640/A 11/2018

NOTES: (continued)

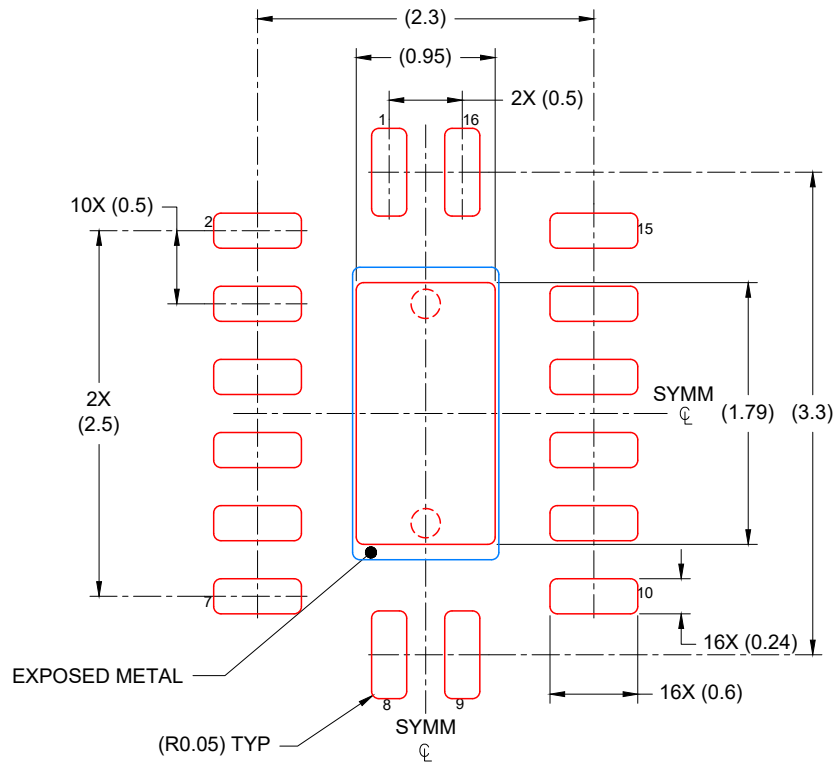
4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slue271).
5. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.

EXAMPLE STENCIL DESIGN

BQB0016A

WQFN - 0.8 mm max height

PLASTIC QUAD FLAT PACK-NO LEAD



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL

EXPOSED PAD
85% PRINTED COVERAGE BY AREA
SCALE: 20X

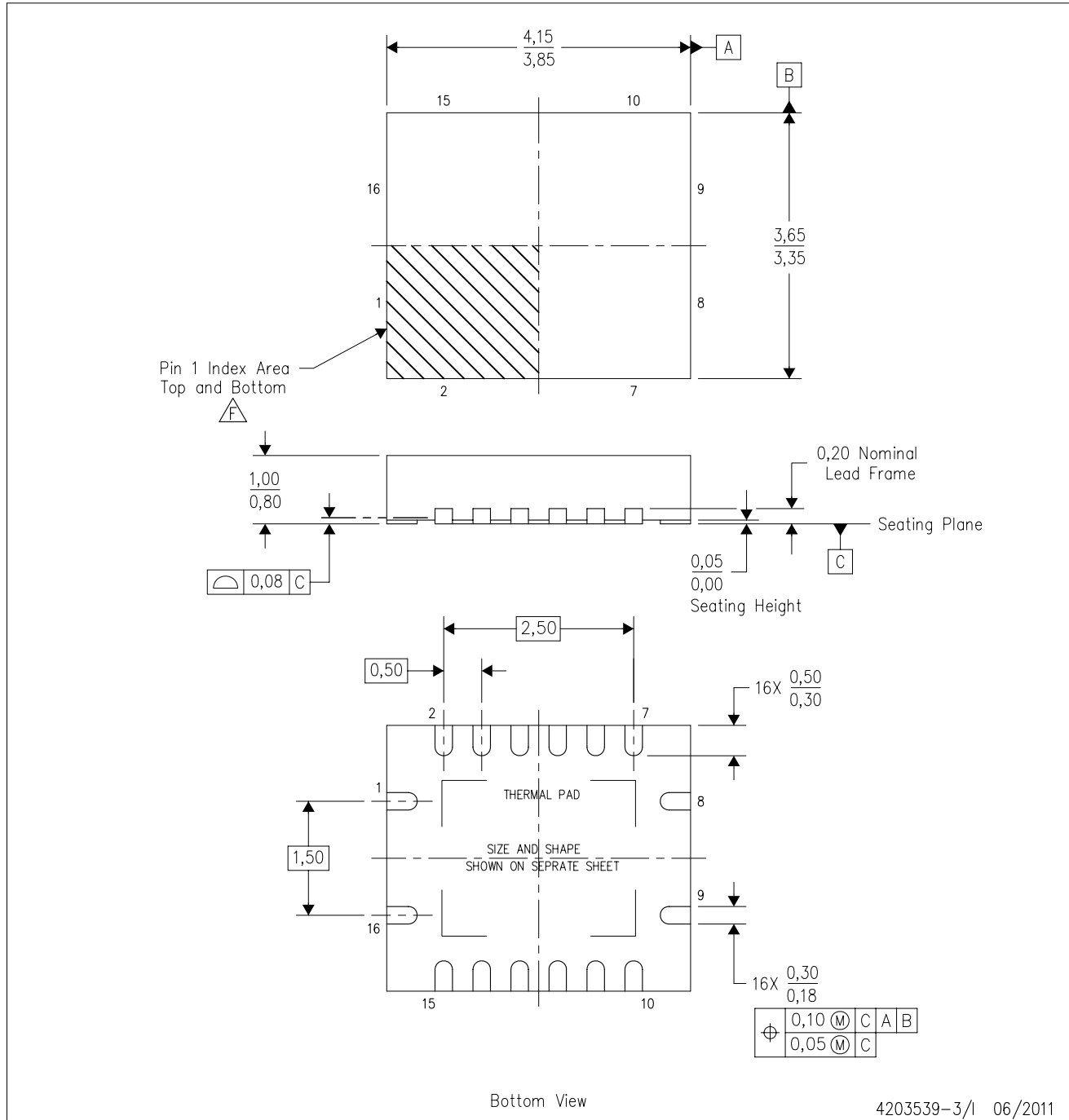
4224640/A 11/2018

NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

RGY (R-PVQFN-N16)

PLASTIC QUAD FLATPACK NO-LEAD



4203539-3/I 06/2011

- NOTES:
- All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.
 - This drawing is subject to change without notice.
 - QFN (Quad Flatpack No-Lead) package configuration.
 - The package thermal pad must be soldered to the board for thermal and mechanical performance.
 - See the additional figure in the Product Data Sheet for details regarding the exposed thermal pad features and dimensions.
- F** Pin 1 identifiers are located on both top and bottom of the package and within the zone indicated. The Pin 1 identifiers are either a molded, marked, or metal feature.
- Package complies to JEDEC MO-241 variation BA.

RGY (R-PVQFN-N16)

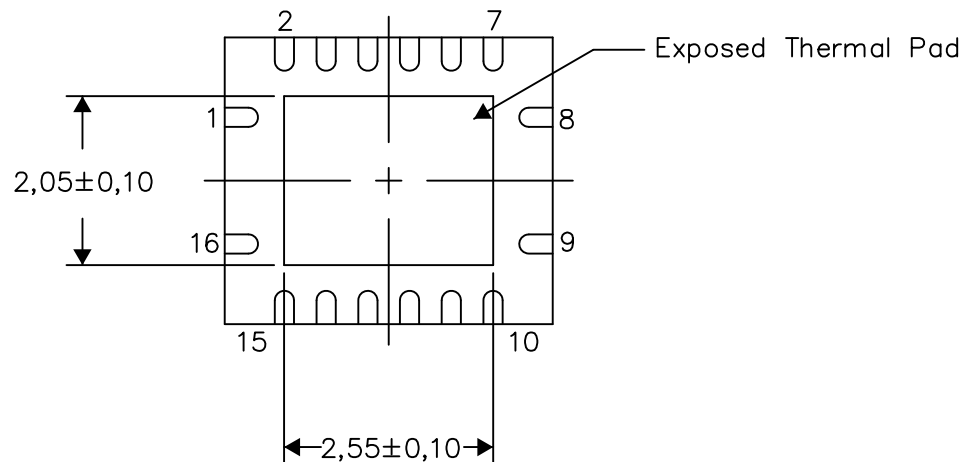
PLASTIC QUAD FLATPACK NO-LEAD

THERMAL INFORMATION

This package incorporates an exposed thermal pad that is designed to be attached directly to an external heatsink. The thermal pad must be soldered directly to the printed circuit board (PCB). After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For information on the Quad Flatpack No-Lead (QFN) package and its advantages, refer to Application Report, QFN/SON PCB Attachment, Texas Instruments Literature No. SLUA271. This document is available at www.ti.com.

The exposed thermal pad dimensions for this package are shown in the following illustration.



Bottom View

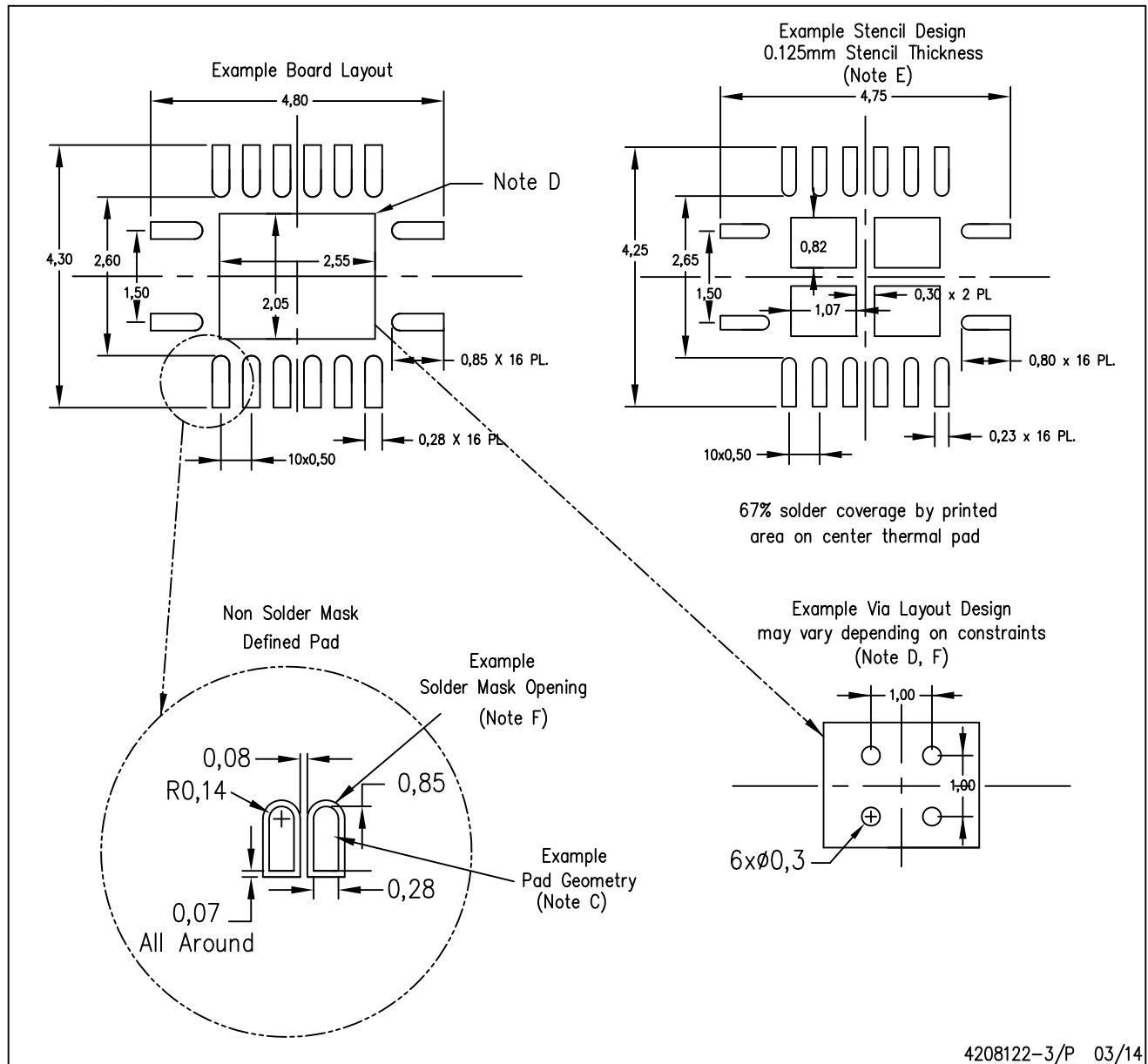
Exposed Thermal Pad Dimensions

4206353-3/P 03/14

NOTE: All linear dimensions are in millimeters

RGY (R-PVQFN-N16)

PLASTIC QUAD FLATPACK NO-LEAD



- NOTES:
- All linear dimensions are in millimeters.
 - This drawing is subject to change without notice.
 - Publication IPC-7351 is recommended for alternate designs.
 - This package is designed to be soldered to a thermal pad on the board. Refer to Application Note, Quad Flat-Pack QFN/SON PCB Attachment, Texas Instruments Literature No. SLUA271, and also the Product Data Sheets for specific thermal information, via requirements, and recommended board layout. These documents are available at www.ti.com <<http://www.ti.com>>.
 - Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC 7525 for stencil design considerations.
 - Customers should contact their board fabrication site for minimum solder mask web tolerances between signal pads.

重要声明和免责声明

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